

# Semiconductor Fundamentals

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# Last Lecture: 3 key points

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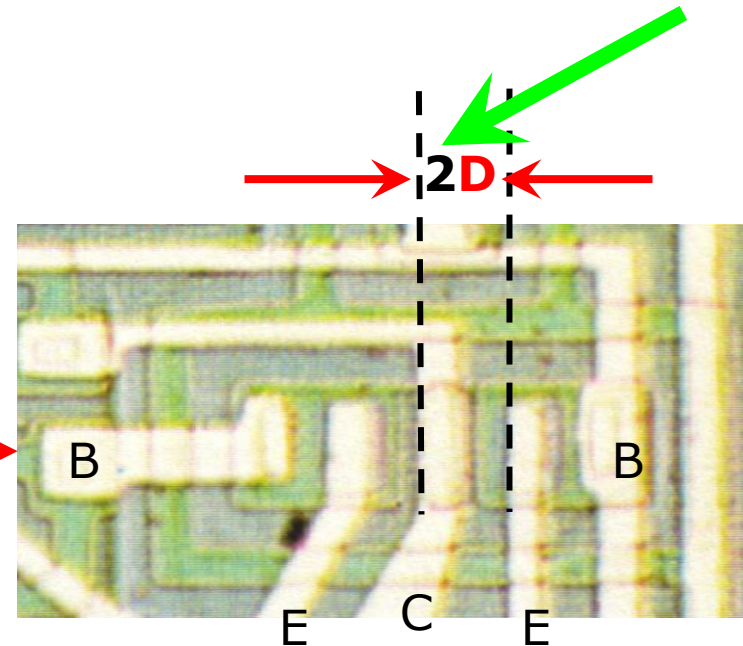
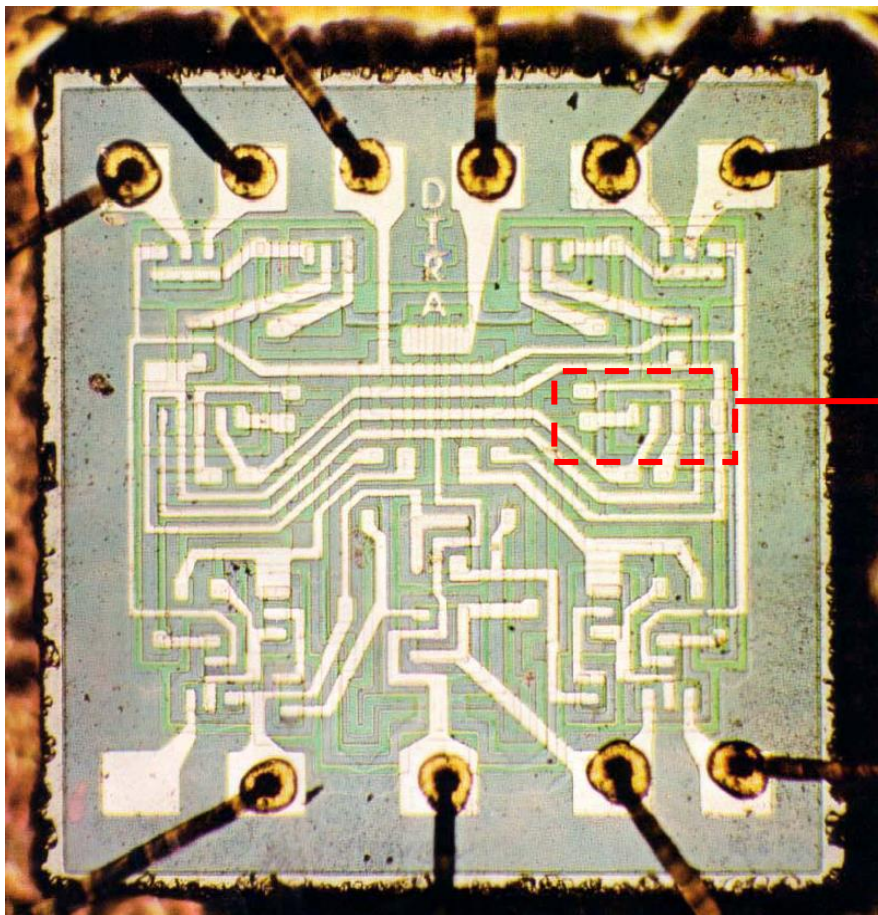
1. Moores' Law
2. Technology **Node** Definition
3. Yield Definition

## 1. Moores' Law:

The **number of transistors** on a chip **doubled** every **18 to 24 months**.

## 2. Technology **Node** Definition

- Images courtesy of Fairchild Semiconductor. Used without permission.



"D" represents IC technology level.  
The names of "D", nowadays:  
"D technology", or  
"Generation D", or "**D node**"

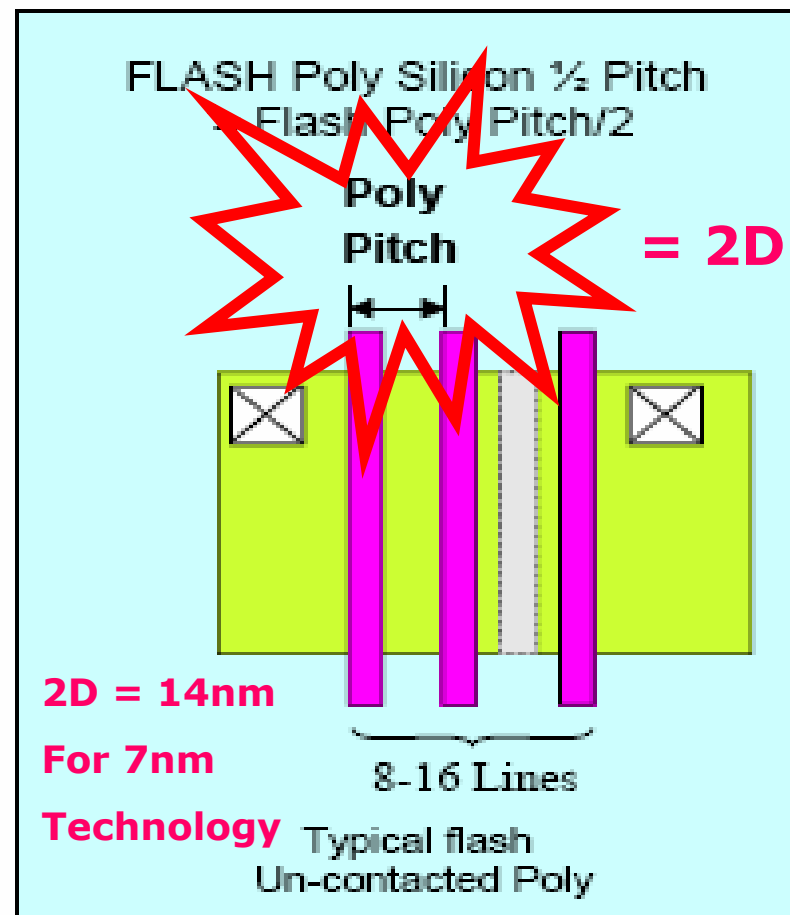
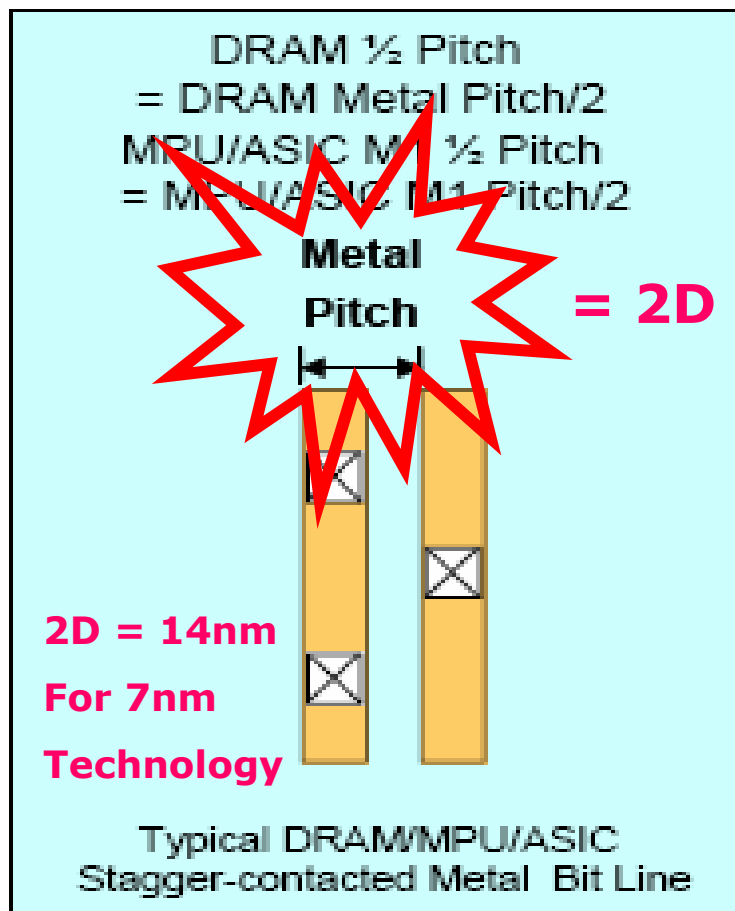
**ITRS:** *<http://www.itrs.net/home.html>*

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- The **I**nternational **T**echnology **R**oadmap for **S**emiconductors, known throughout the world as the **ITRS**, is the fifteen-year assessment of the **semiconductor industry's future technology requirements.**

# ITRS Technology **Node** Definitions

Individual roadmaps are defined for high-performance, low-power, etc.



# 3. Yield

$$\text{Die yield} = \frac{\text{No. of good chips per wafer}}{\text{Total number of chips per wafer}} \times 100\%$$

$$\text{Die cost} = \frac{\text{Wafer cost}}{\text{Dies per wafer} \times \text{Die yield}} \quad \text{Die = Chip}$$

- in Fig.1, the **yield** is 50% and the die **cost** is £250 (If this wafer costs £500).
- In Fig.2, the **yield** is 87% and the chip **cost** is £36 (If this wafer costs £500).

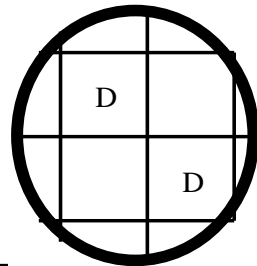
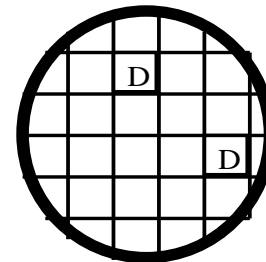


Fig.1



Technology node ↓

Fig.2

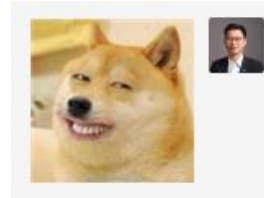
# Chapter 2 Outline

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## Semiconductor Fundamentals-(I)

2.1 Atomic structures

2.2 Crystal structures



## Semiconductor Fundamentals-(II)

2.3 Energy bands

2.4 The doping of semiconductors

## Semiconductor Fundamentals-(III)

2.5 Boltzmann approximation &  $E_F$ ,  $n$ ,  $p$

2.6 Carrier drift and diffusion

# Semiconductor Fundamentals – (I)

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**2.1 Atomic structures**

**2.2 Crystal structures**

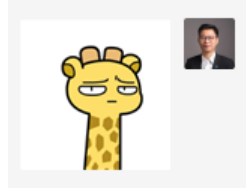


# 2.1

# Atomic Structures

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- **Elements**



- Bohr's theory – orbits
- Distribution of electrons
  - Valence electrons
- Bonding
  - Ionised bond
  - Covalent bond

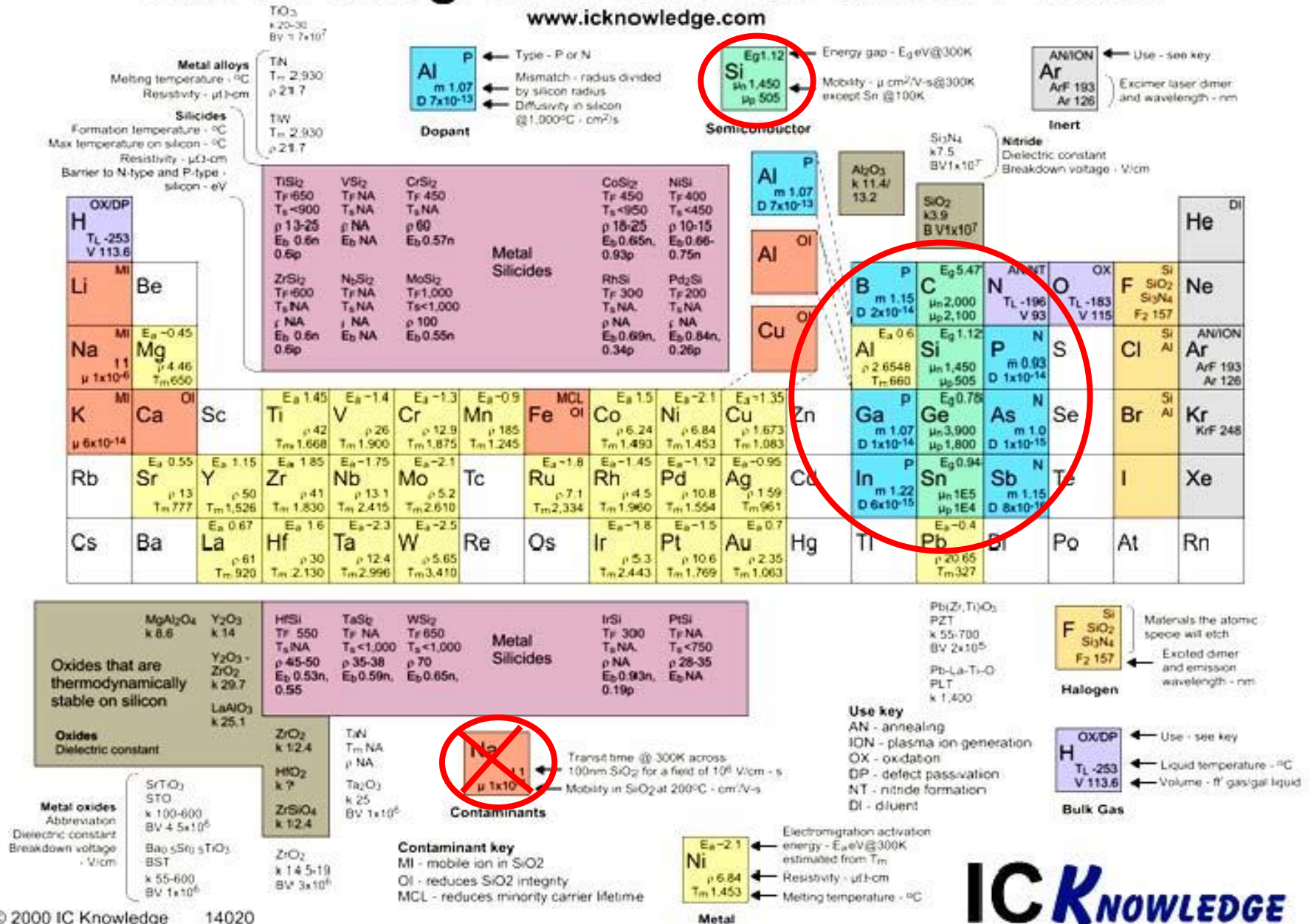
Atomic masses in parentheses are those of the most stable or common isotope.

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57 <b>La</b> Lanthanum 138.9055	58 <b>Ce</b> Cerium 140.116	59 <b>Pr</b> Praseodymium 140.90765	60 <b>Nd</b> Neodymium 144.24	61 <b>Pm</b> Promethium (145)	62 <b>Sm</b> Samarium 150.36	63 <b>Eu</b> Europium 151.964	64 <b>Gd</b> Gadolinium 157.25	65 <b>Tb</b> Terbium 158.92534	66 <b>Dy</b> Dysprosium 162.500	67 <b>Ho</b> Holmium 164.93032	68 <b>Er</b> Erbium 167.259	69 <b>Tm</b> Thulium 168.93421	70 <b>Yb</b> Ytterbium 173.04	71 <b>Lu</b> Lutetium 174.967		
72 <b>Hf</b> Hafnium 178.49	73 <b>Ta</b> Tantalum 180.94788	74 <b>W</b> Tungsten 183.84	75 <b>Re</b> Rhenium 186.207	76 <b>Os</b> Osmium 190.23	77 <b>Ir</b> Iridium 192.222	78 <b>Pt</b> Platinum 195.084	79 <b>Au</b> Gold 196.96657	80 <b>Hg</b> Mercury 200.59	81 <b>Tl</b> Thallium 204.38	82 <b>Pb</b> Lead 207.2	83 <b>Bi</b> Bismuth 208.9804	84 <b>Po</b> Polonium 209	85 <b>At</b> Astatine 210	86 <b>Rn</b> Radon 222		
87 <b>Fr</b> Francium 223	88 <b>Ra</b> Radium 226	89 <b>Ac</b> Actinium 227	90 <b>Th</b> Thorium 232.0381	91 <b>Pa</b> Protactinium 231.03688	92 <b>U</b> Uranium 238.02891	93 <b>Np</b> Neptunium (237)	94 <b>Pu</b> Plutonium (244)	95 <b>Am</b> Americium (243)	96 <b>Cm</b> Curium (247)	97 <b>Bk</b> Berkelium (247)	98 <b>Cf</b> Californium (251)	99 <b>Es</b> Einsteinium (252)	100 <b>Fm</b> Fermium (257)	101 <b>Md</b> Mendelevium (258)	102 <b>No</b> Nobelium (259)	103 <b>Lr</b> Lawrencium (262)

# Silicon Integrated Circuit Periodic Table

www.icknowledge.com



# Semiconductor Materials

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	III	IV	V	
	Boron (B)	Carbon (C)		
• • •	Aluminum (Al)	Silicon (Si)	Phosphorus (P)	• • •
	Gallium (Ga)	Germanium (Ge)	Arsenic (As)	
		• • •	Antimony (Sb)	



# Semiconductor Materials

Elemental: *Si, Ge, C*

Compound: *IV-IV : SiC*  
*III-V : GaAs*  
*GaN*  
*II-VI : CdSe*

Alloy: *Si<sub>1-x</sub>Ge<sub>x</sub>*

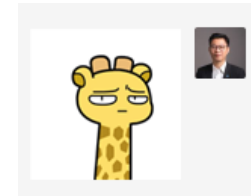
*Al<sub>x</sub>Ga<sub>1-x</sub>As*

	12	13	14	15	16	17	18
							2 He
		5 B	6 C	7 N	8 O	9 F	10 Ne
		13 Al	14 Si	15 P	16 S	17 Cl	18 Ar
30 Zn	31 Ga	32 Ge	33 As	34 Se	35 Br	36 Kr	
48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe	
80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn	
112 Uub		114 Uuq		116 Uuh		118 Uuo	
66 Dy	67 Ho	68 Er	69 Tm	70 Yb			
98 Cf	99 Es	100 Fm	101 Md	102 No			

# 2.1 Atomic Structures

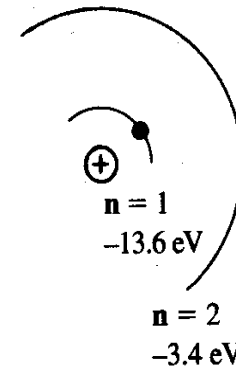
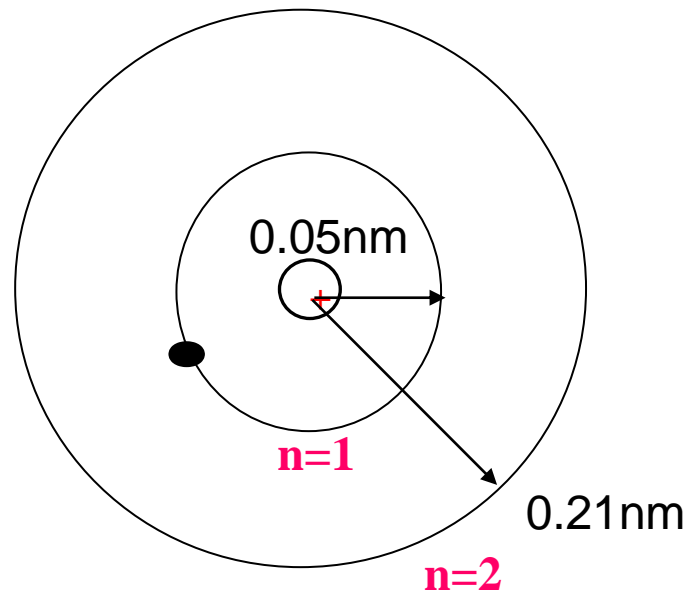
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- Elements
- **Bohr's theory – orbits**
- Distribution of electrons
  - Valence electrons
- Bonding
  - Ionised bond
  - Covalent bond



# Bohr's Theory - Orbits

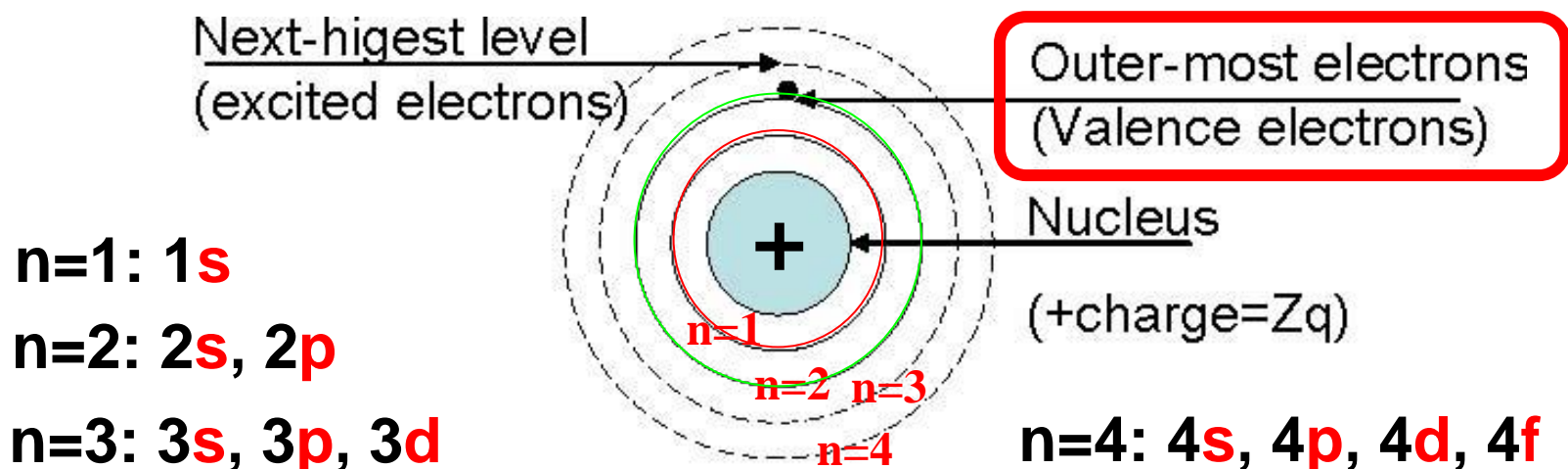
- The electrons of an atom can only stay on a number of orbits. **The radius of orbits changes discontinuously.**
- For example, **hydrogen atom**,



- The orbit with **smaller radius** has **lower energy**.

# Orbits <http://winter.group.shef.ac.uk/orbitron/>

- Electrons reside in stable configurations (orbits, orbitals)
- These orbitals are numbered (in order of increasing energy): 1s 2s 2p 3s 3p 3d 4s 4p 4d 4f ...
- “s” levels: **two** electron states
- Each “p” level is 3 fold degenerate: **six** electron states
- Historical: “s” was chosen because the optical emission related to transitions for these levels gives “sharp” lines (similarly: “principal”, “diffuse” etc.)

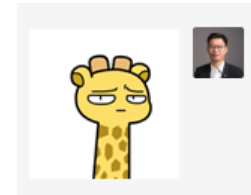




# 2.1 Atomic Structures

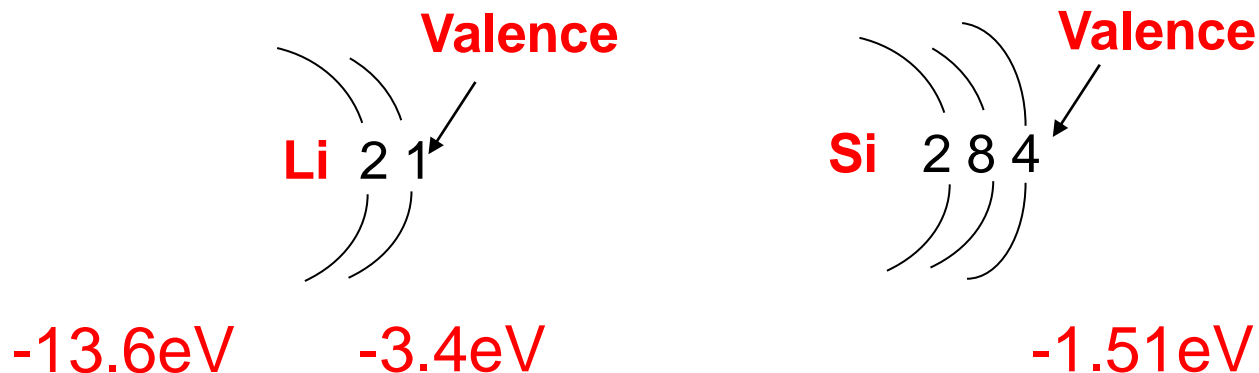
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- Elements
- Bohr's theory – orbits
- **Distribution of electrons**
  - Valence electrons
- Bonding
  - Ionised bond
  - Covalent bond

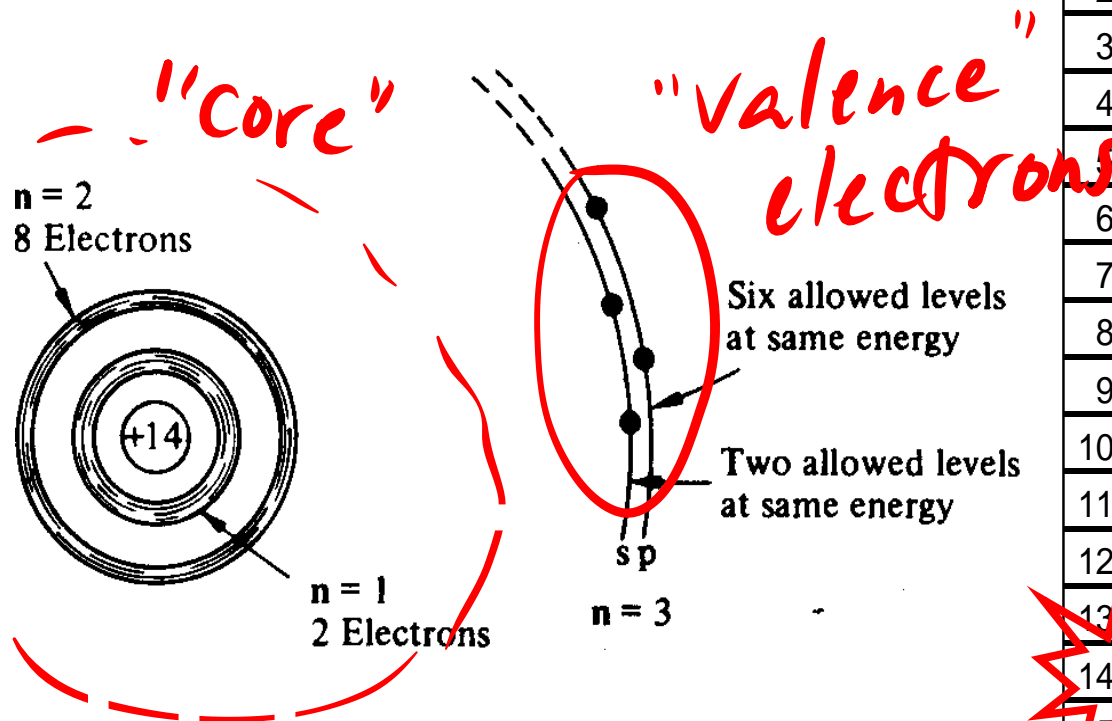


# Distribution of electrons in atoms

- **Maximum number of electrons in an orbit is fixed**
  - 1<sup>st</sup> orbit: 2 (1s)
  - 2<sup>nd</sup> orbit: 8 (2s, 2p)      (3<sup>rd</sup> orbit: 3s, 3p, 3d)
- Orbit with lowest energy is filled first, since the lower energy, the more stable.
- The orbit with smaller radius has lower energy.
- Electrons in **the outmost orbit**: 'valence electrons'.
- Property of atoms depends on valence electrons



# From Hydrogen to **Silicon**

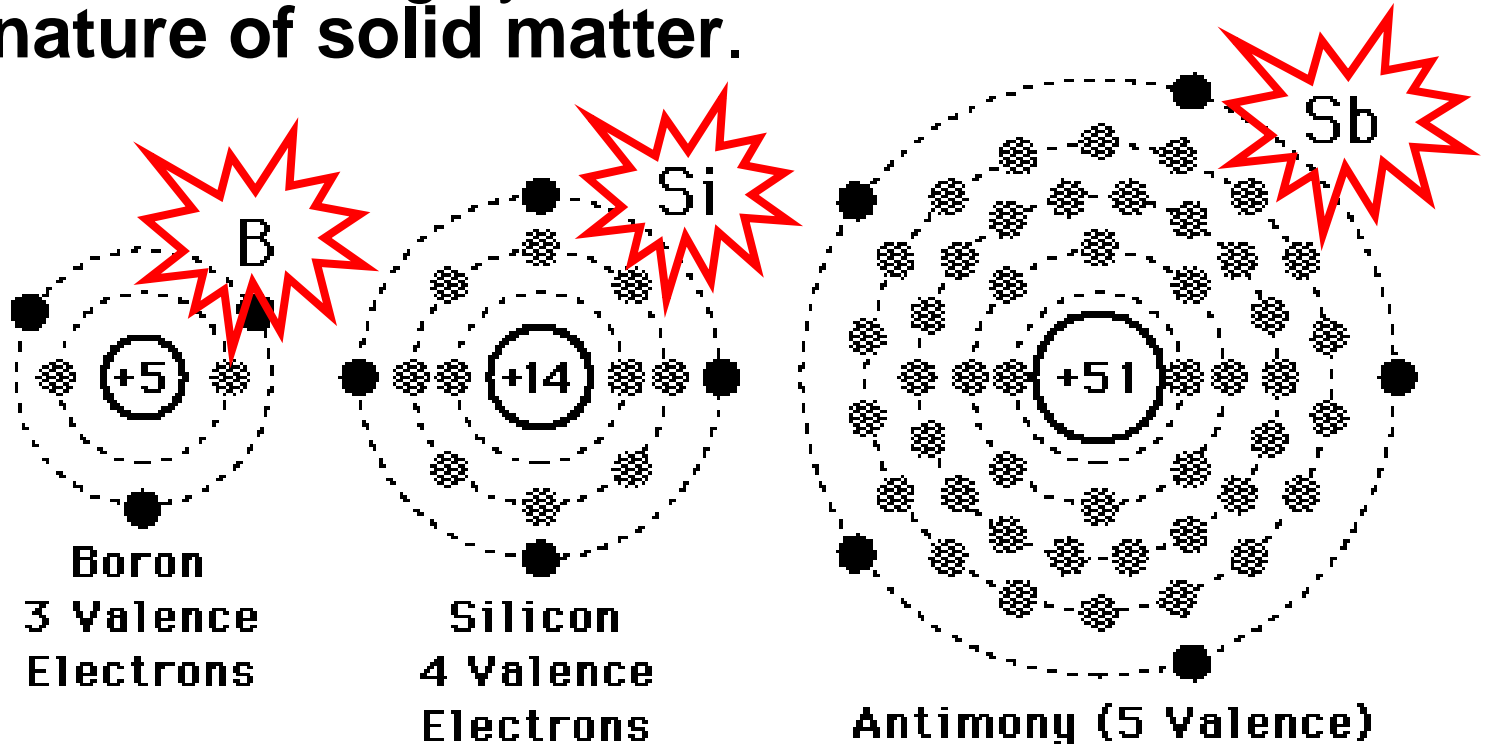


$n=3$ : 3s, 3p, 3d

Z	Name	# of Electrons						Notation
		1	2		3			
		1s	2s	2p	3s	3p	3d	
1	H	1						$1s^1$
2	He	2						$1s^2$
3	Li	2	1					$1s^2 2s^1$
4	Be	2	2					$1s^2 2s^2$
5	B	2	2	1				$1s^2 2s^2 2p^1$
6	C	2	2	2				$1s^2 2s^2 2p^2$
7	N	2	2	3				$1s^2 2s^2 2p^3$
8	O	2	2	4				$1s^2 2s^2 2p^4$
9	F	2	2	5				$1s^2 2s^2 2p^5$
10	Ne	2	2	6				$1s^2 2s^2 2p^6$
11	Na	2	2	6	1			$1s^2 2s^2 2p^6 3s^1$
12	Mg	2	2	6	2			$1s^2 2s^2 2p^6 3s^2$
13	Al	2	2	6	2	1		$1s^2 2s^2 2p^6 3s^2 3p^1$
14	Si	2	2	6	2	2		$1s^2 2s^2 2p^6 3s^2 3p^2$
15	P	2	2	6	2	3		$1s^2 2s^2 2p^6 3s^2 3p^3$
16	S	2	2	6	2	4		$1s^2 2s^2 2p^6 3s^2 3p^4$
17	Cl	2	2	6	2	5		$1s^2 2s^2 2p^6 3s^2 3p^5$
18	Ar	2	2	6	2	6		$1s^2 2s^2 2p^6 3s^2 3p^6$

# Valence Electrons of **B**, **Si** & **Sb**

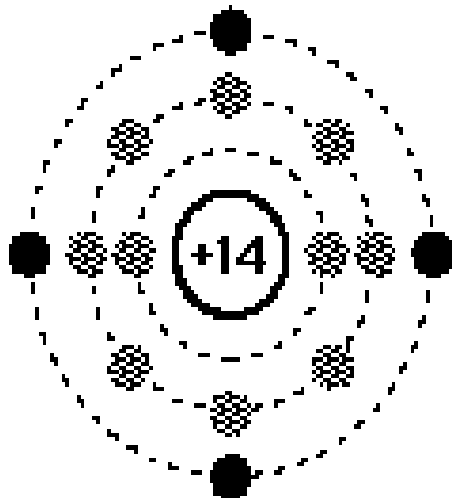
- The electrons in the **outermost shell** of an atom are called **valence electrons**; they dictate the **nature of chemical reactions of atom** and largely determine the **electrical nature of solid matter**.



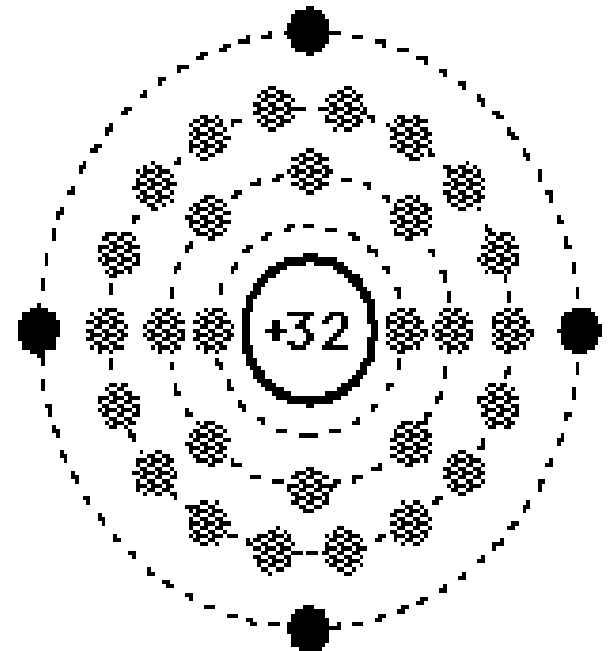
# Valence Electrons of **Si** & **Ge**

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- **Solid state electronics** arises from the **unique properties** of **silicon** and **germanium**, each of which has **4 valence electrons** and which form crystal lattices.



Silicon

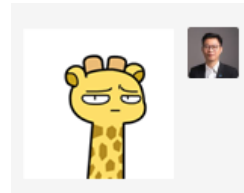


Germanium

# 2.1 Atomic Structures

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- Elements
- Bohr's theory – orbits
- Distribution of electrons
  - Valence electrons
- **Bonding**
  - Ionised bond
  - Covalent bond

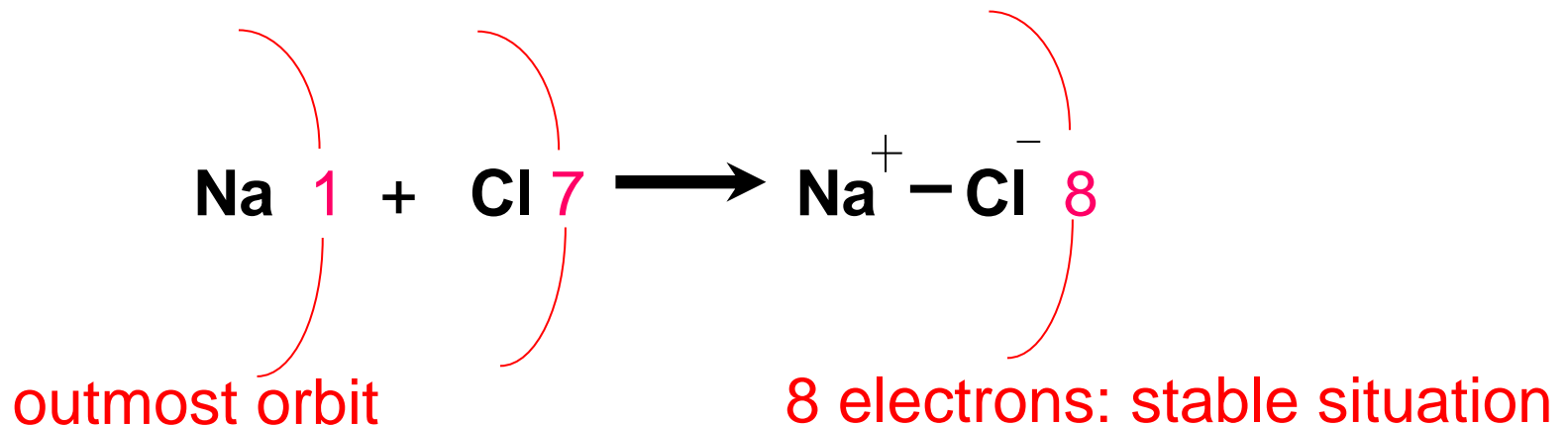


# Bonding

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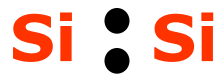
- An **unstable** atom can achieve a **quasi-stable** structure by **bonding with other atoms**.
- **Ionized bonds:**

The atoms are ionized first and then bonded through **electrostatic force**.

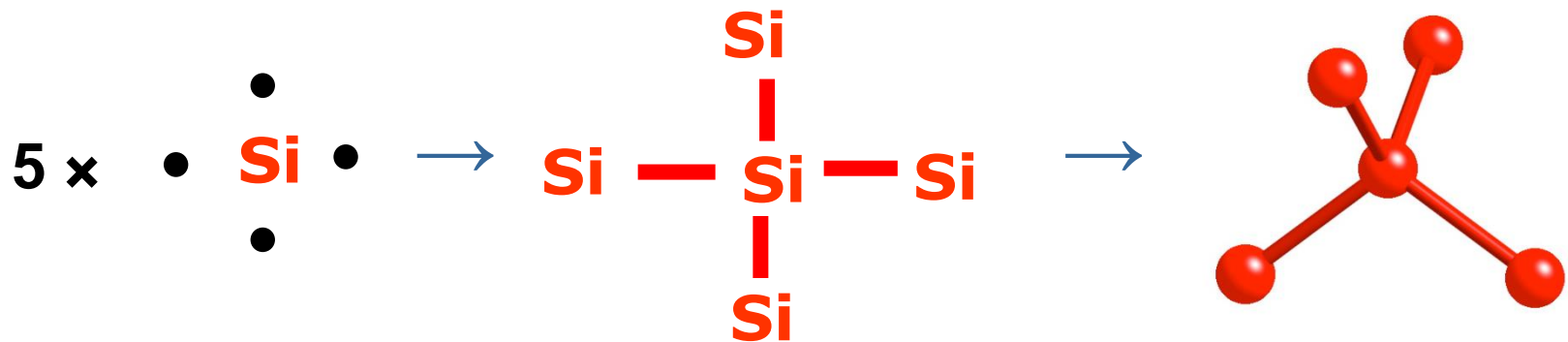


# Covalent bonds

- Valence electrons are shared
- Notation of a covalent bond (can't be “seen”)

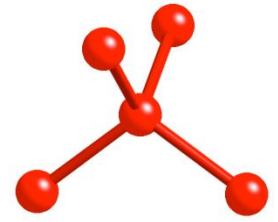


- Si shares its **4 valence electrons** with **4 other Si atoms** by forming covalent bonds.

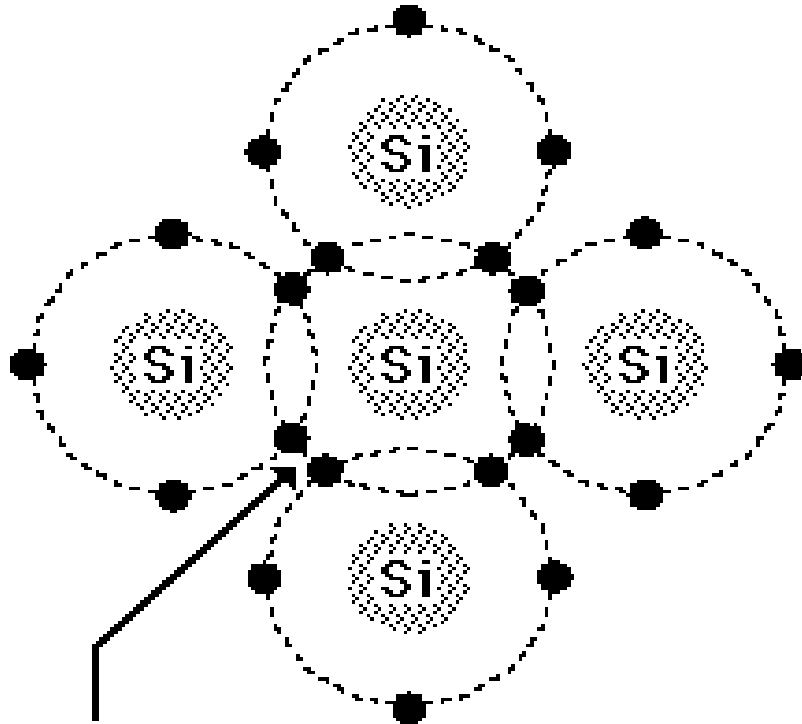




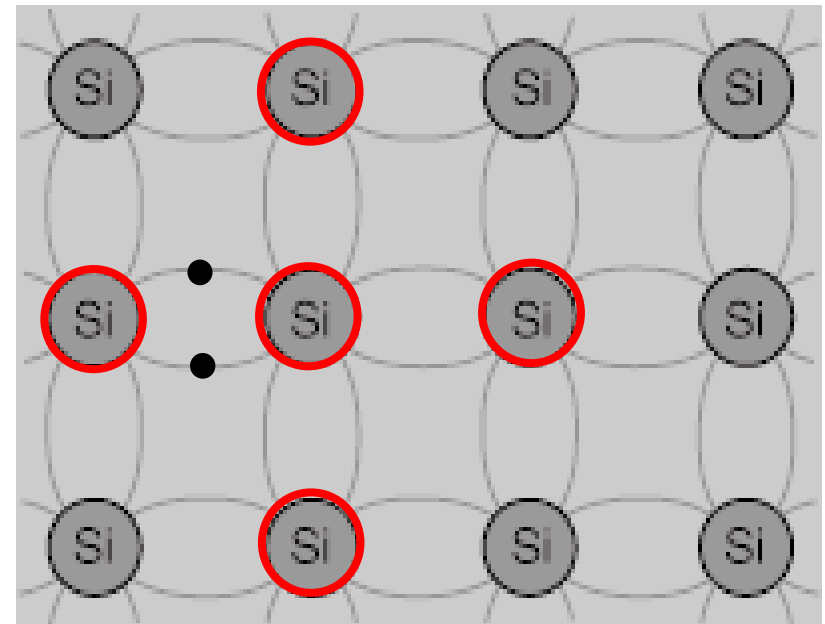
# Covalent bonds



- The bonds are of **equal length** and **angular separation** to produce a **crystal structure**.



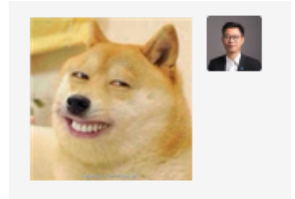
Shared electrons  
of a covalent  
bond.



## 2.2 Crystal Structures

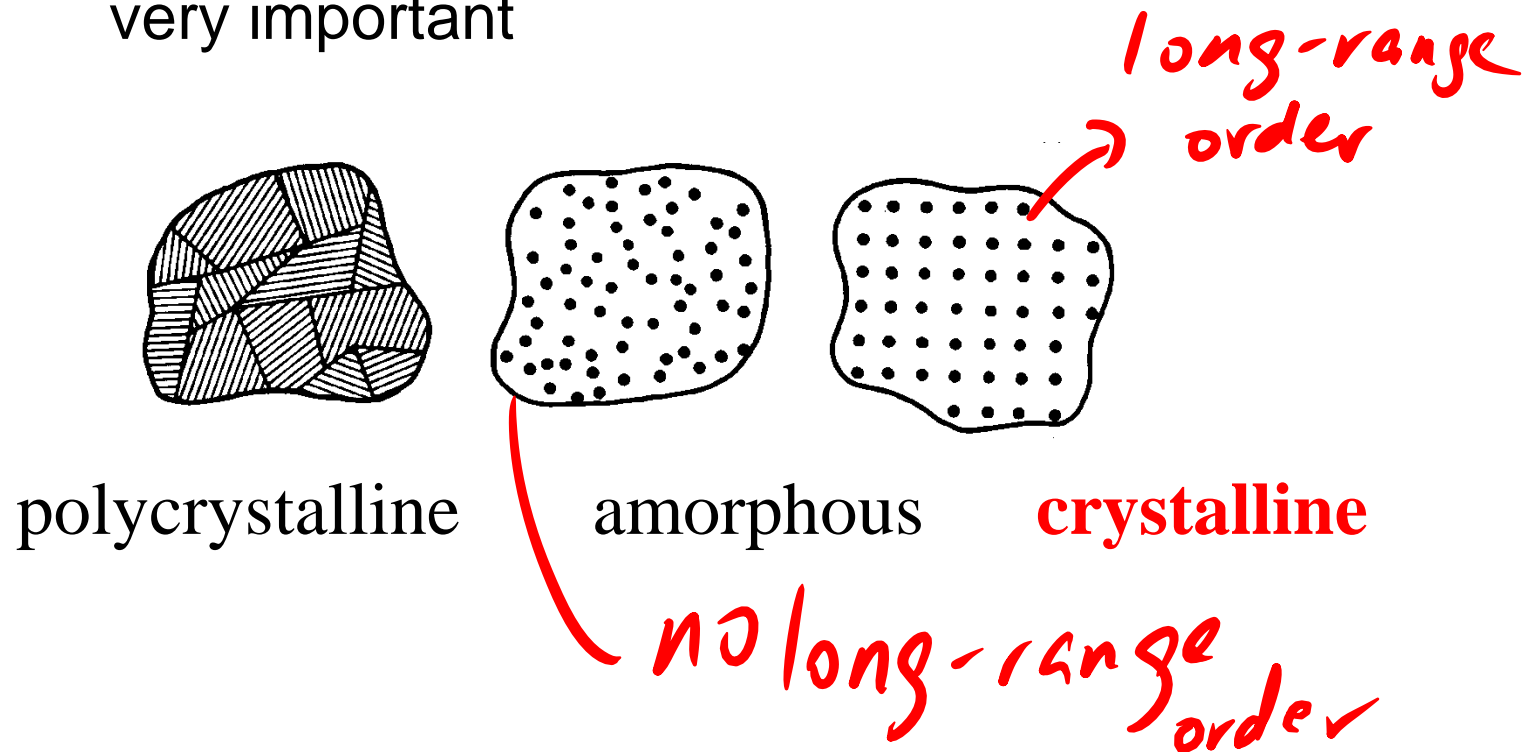
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- **General material properties**
- Crystal structures
- Crystallographic notation
- Bohr's theory – energy level & band



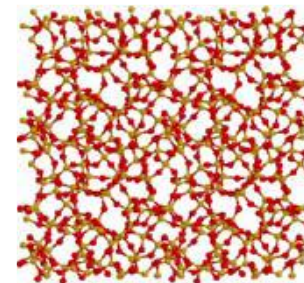
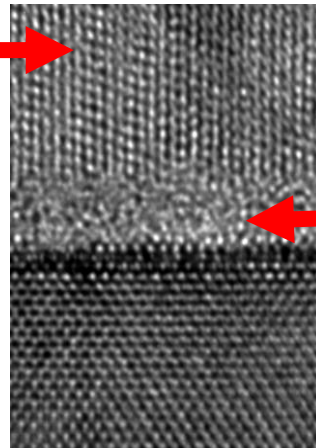
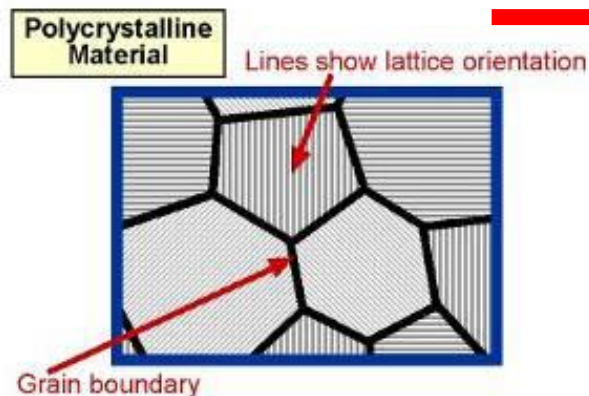
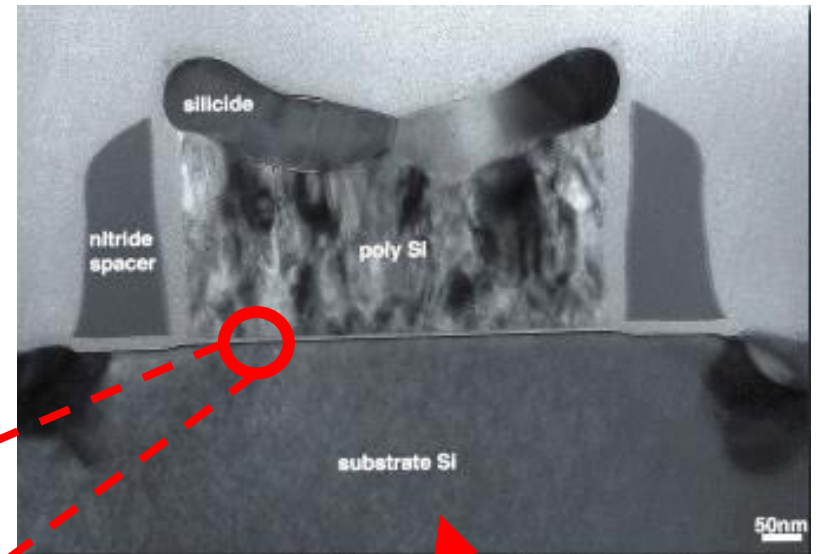
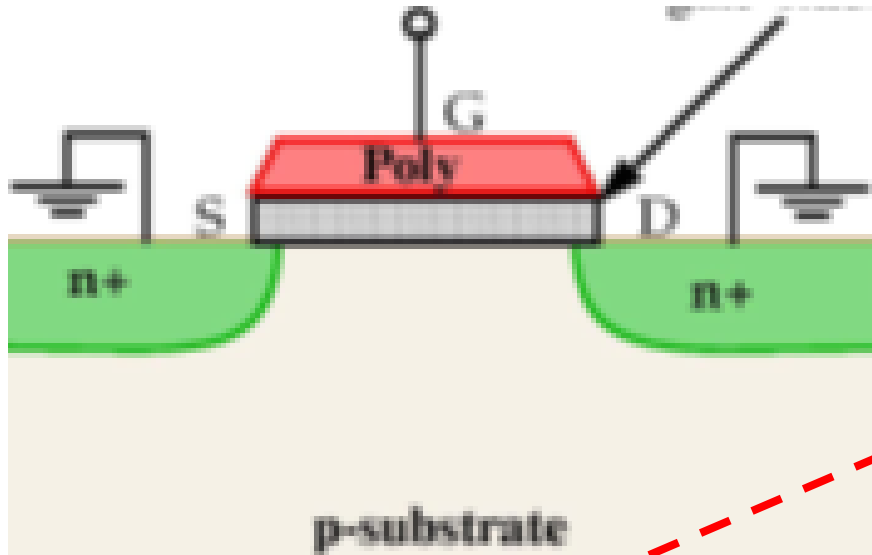
# Material Properties

- Generally **crystalline** in structure for IC devices
  - In recent years, however, **non-crystalline** semiconductors have become commercially very important

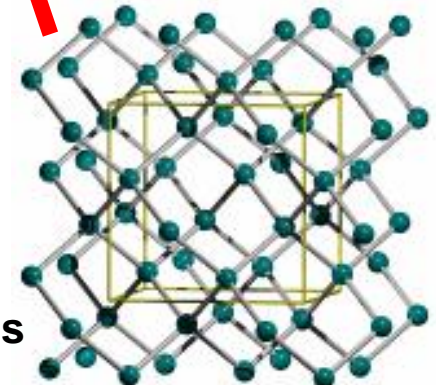


# Material Properties: Example

## Transmission Electron Microscope



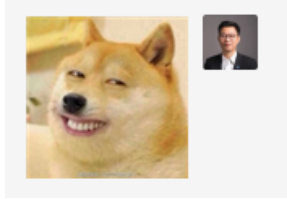
Amorphous Materials



Single-Crystal Material 28

## 2.2 Crystal Structures

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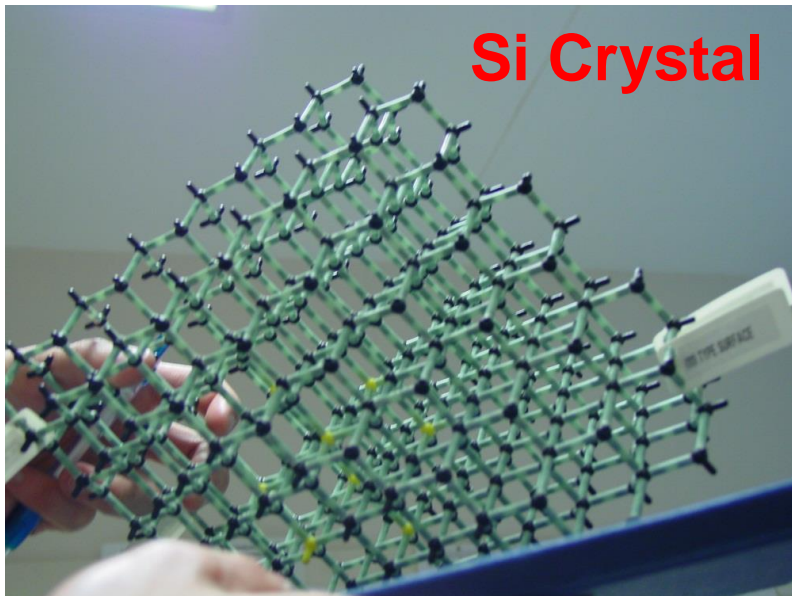
- General material properties
- **Crystal structures** 
- Crystallographic notation
- Bohr's theory – energy level & band

# Silicon Crystallography

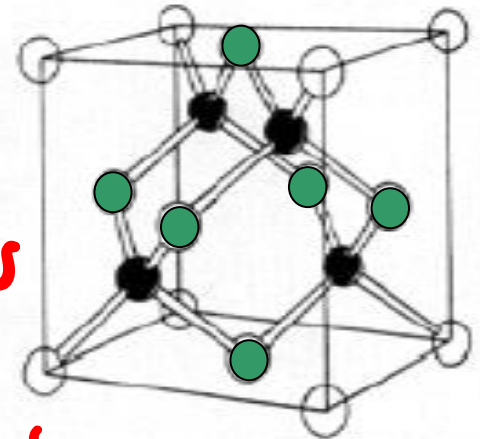
- **Lattice:** periodic arrangement of atoms in a crystal
- **Unit Cell:** smallest volume segment representative of entire lattice

**Crystal : Atoms + Lattice**

- **Silicon Lattice = Diamond Lattice:** atoms with four covalent bonds, cubic lattice

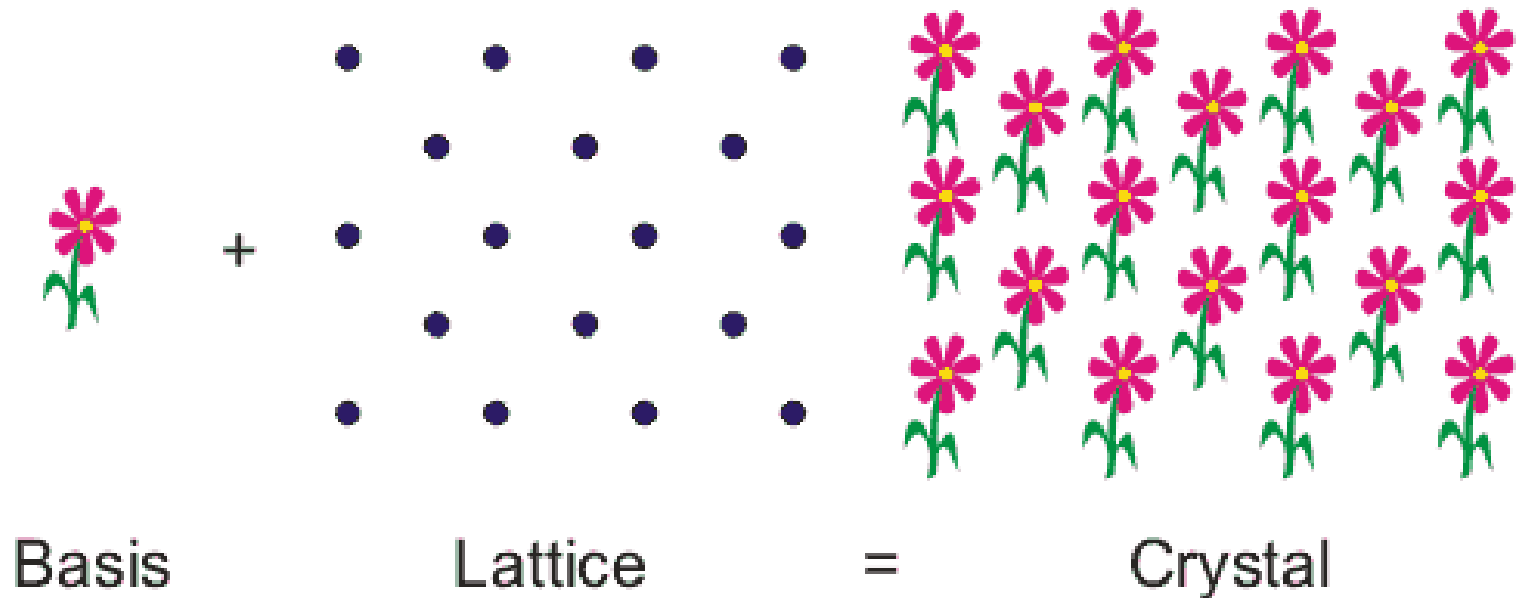


8 corner atoms  
6 face atoms  
4 interior atoms



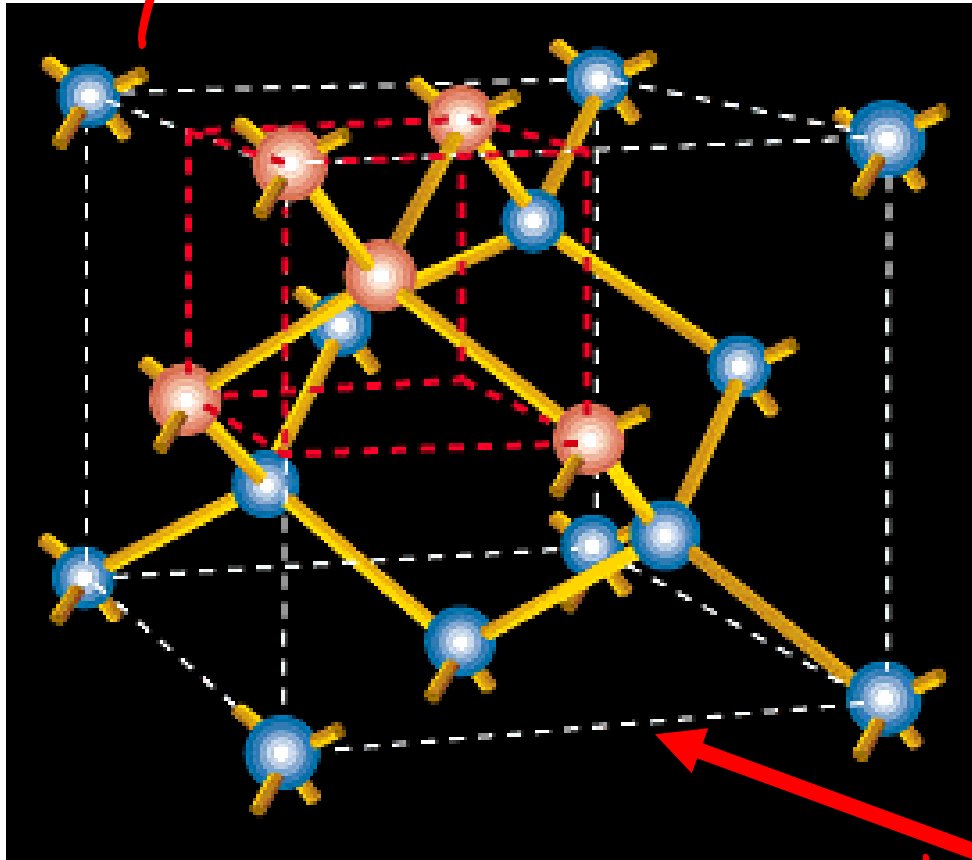
# Lattice and Crystal

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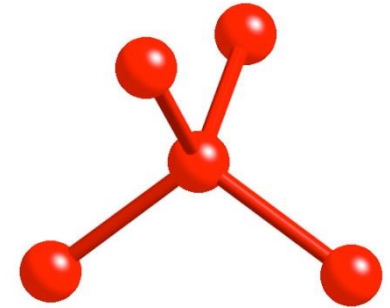
A **crystal** can be thought of as being like **wallpaper**. The motif is analogous to the basis and the arrangement of the motif over the surface is like the **lattice**.

# The Si Crystal: Unit Cell



$\leftarrow a \rightarrow$

“diamond cubic” lattice



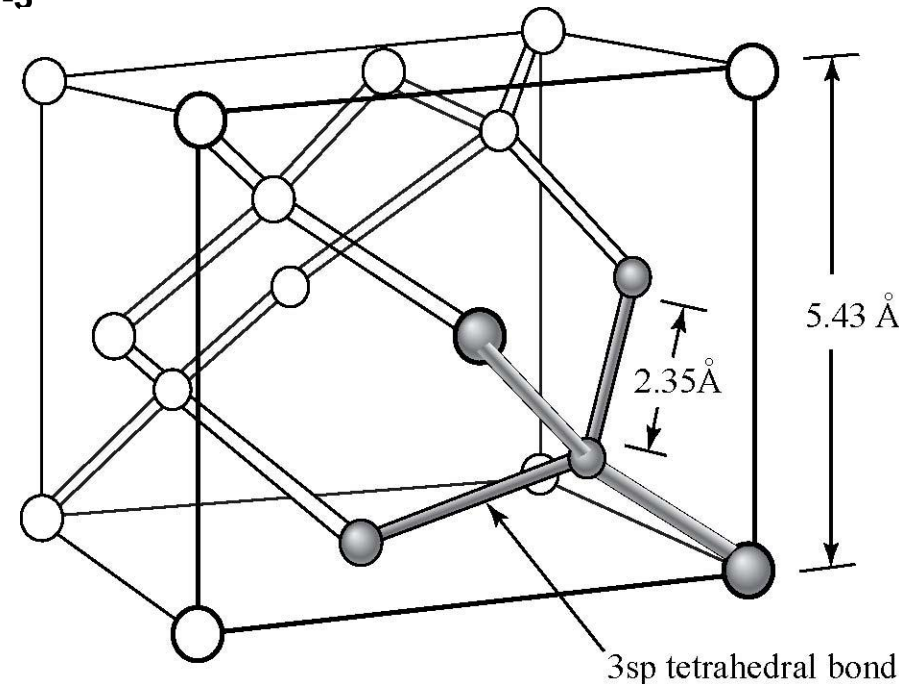
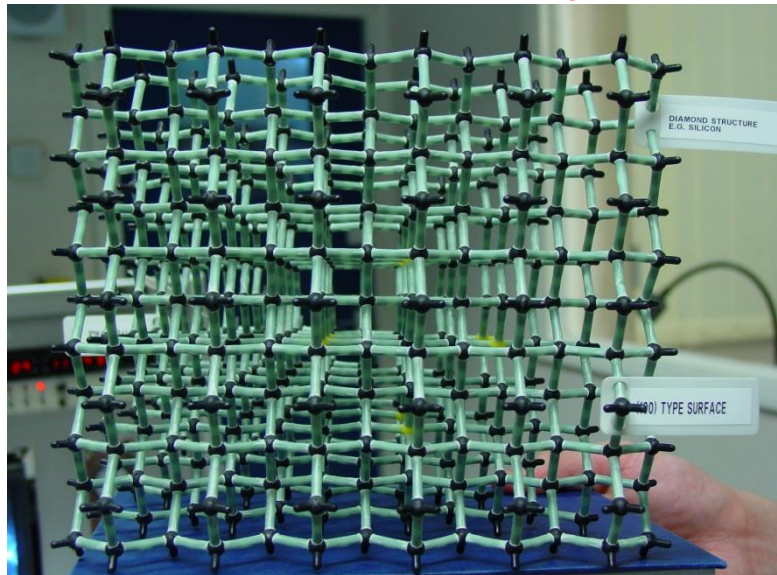
- Each Si atom has 4 nearest neighbors
- Lattice Constant  
= 5.431 Å  
= 0.5431 nm

“diamond lattice”



# Silicon crystal structure

- **Silicon** is a **crystalline** material: – long range atomic arrangement
- **Diamond lattice**: – atoms tetrahedrally bonded by **sharing valence electrons** (covalent bonding)
- Each atom shares **8 electrons**: – low energy and **stable situation**
- **Si atomic density**:  $5 \times 10^{22} \text{ cm}^{-3}$

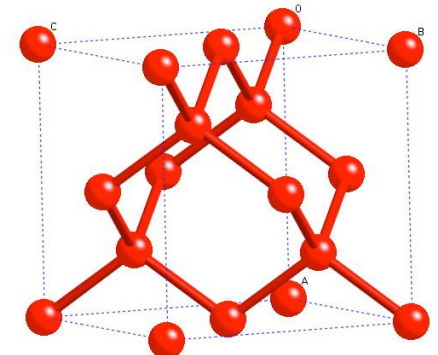
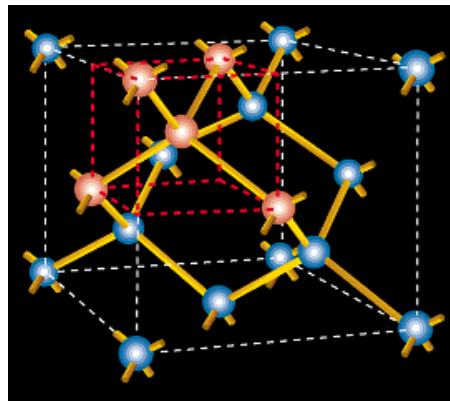
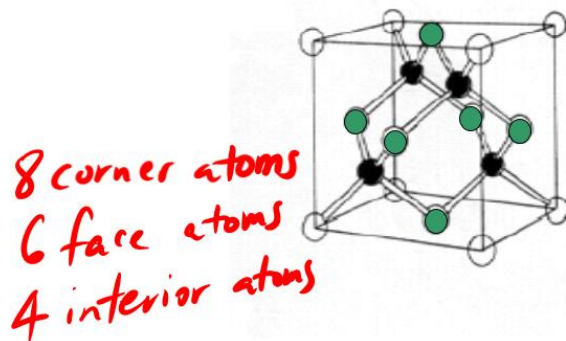


$$\frac{\# \text{Atoms}}{\text{Volume}} = \frac{8 \times 1/8 + 6 \times 1/2 + 4}{a_0^3} = \frac{8}{(5.43 \times 10^{-8} \text{ cm})^3} = 5 \times 10^{22} \text{ cm}^{-3}$$

**HW-1**

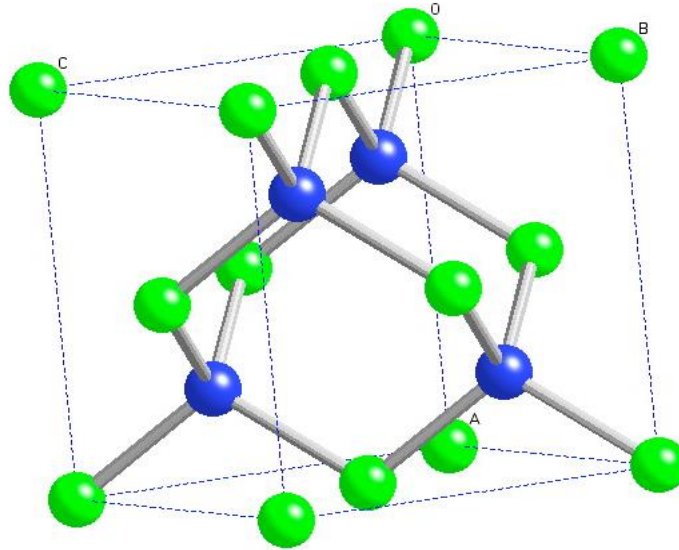
# Silicon crystal structure: **Summary**

- **Silicon atoms** form **covalent bonds** and can crystallize into a **regular lattice**.
- **Silicon atom** has **4** electrons which it can share in **covalent bonds** with its neighbors.
- **Silicon crystallizes** in the same pattern as **diamond**.
- Bold lines between silicon atoms in the lattice illustration indicate nearest-neighbor bonds.



# Compound Semiconductors

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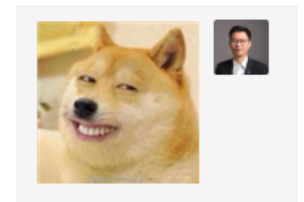


- **“Zinc Blende”** structure  
Simply the diamond structure in which the species of atoms alternate
- **III-V compound semiconductors:** GaAs, GaP, GaN, *etc.*
  - ✓ important for optoelectronics and high-speed ICs

## 2.2 Crystal Structures

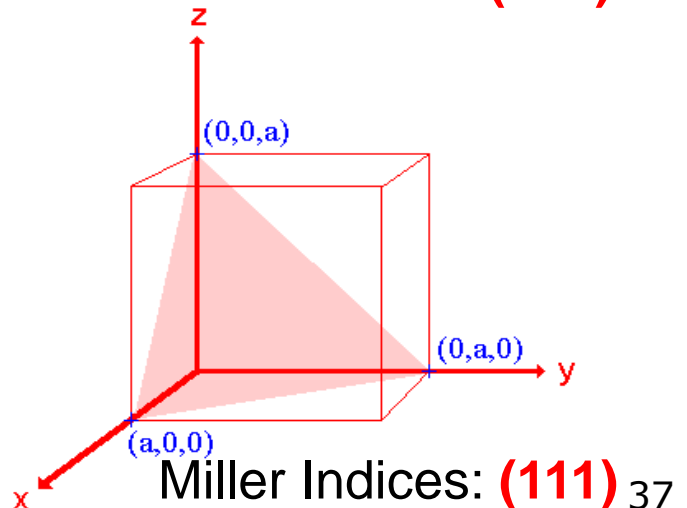
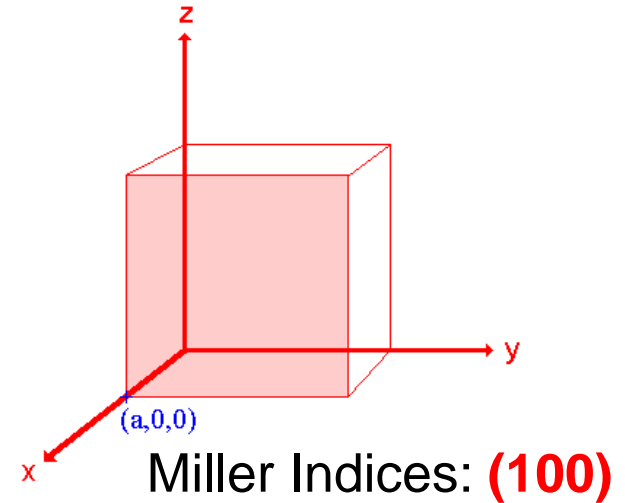
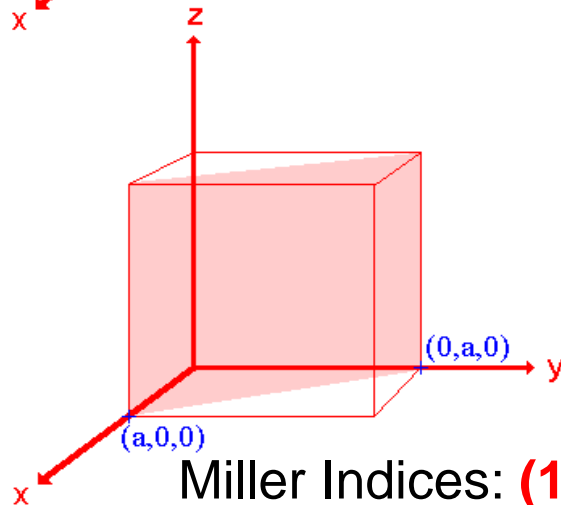
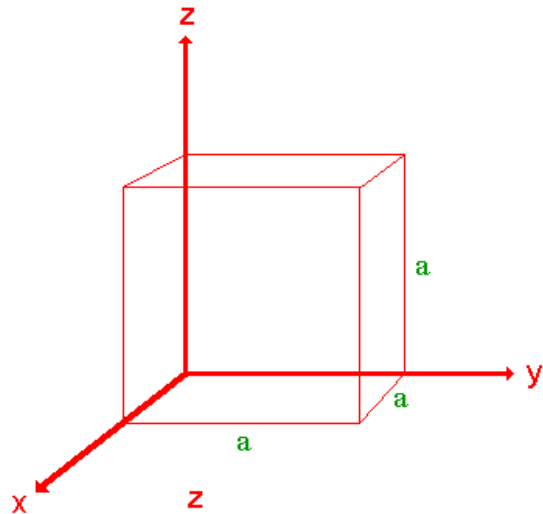
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- General material properties
- Crystal structures
- **Crystallographic notation**
- Bohr's theory – energy level & band



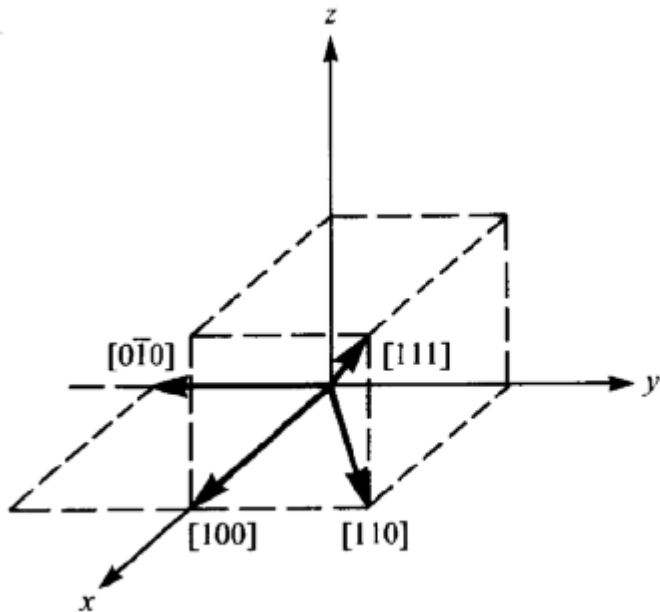
# Crystallographic Notation

- **Miller indices** are a notation system in [crystallography](#) for **planes** and **directions** in [crystal lattices](#).



# Crystallographic Notation: **Directions**

Miller Indices:



Notation	Interpretation
$[h\ k\ l]$	crystal direction
$\langle h\ k\ l \rangle$	equivalent directions

Sample direction vectors and their corresponding Miller indices.

# Crystallographic Notation: **Planes**

## Miller Indices:

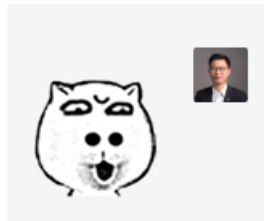
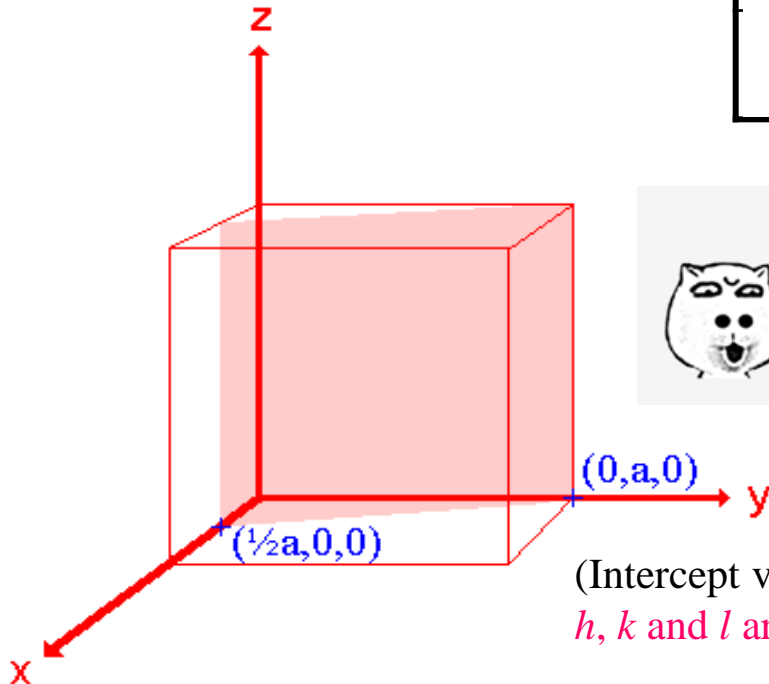
Assignment:

Intercepts:  $\frac{1}{2}a, a, \infty$

Fractional intercepts:  $\frac{1}{2}, 1, \infty$

Miller Indices: (210)

Notation	Interpretation
$(h\ k\ l)$	crystal <b>plane</b>
$\{h\ k\ l\}$	equivalent <b>planes</b>



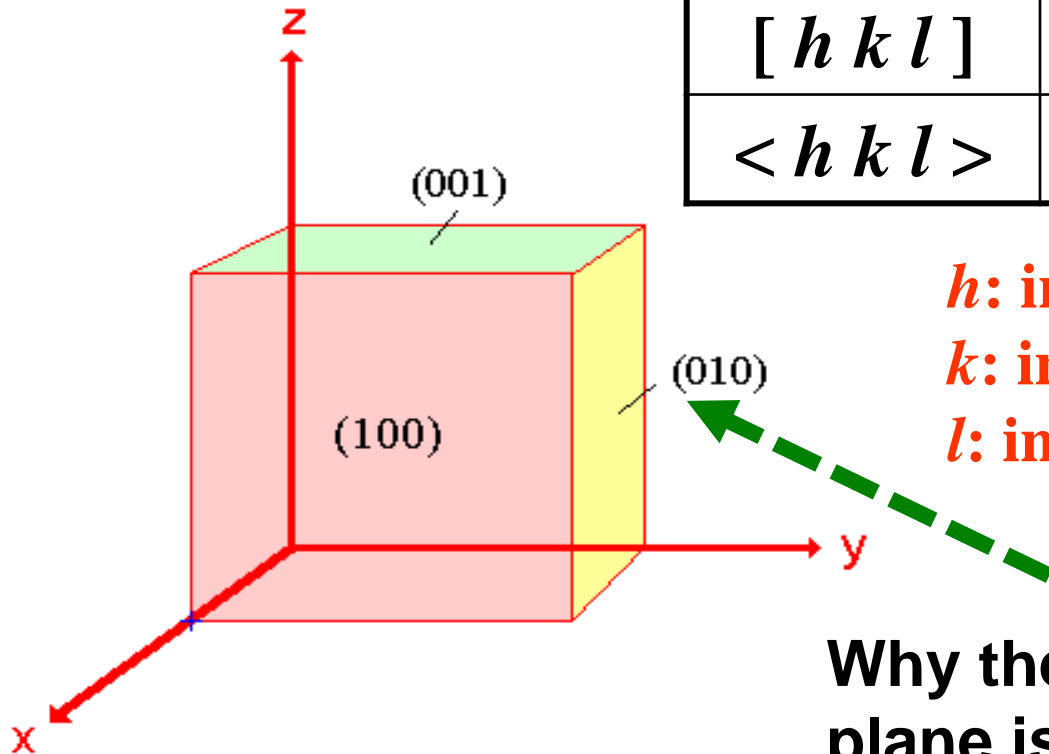
***h***: inverse x-intercept of plane  
***k***: inverse y-intercept of plane  
***l***: inverse z-intercept of plane

(Intercept values are in multiples of the lattice constant;  
*h*, *k* and *l* are reduced/enlarged to 3 integers having the same ratio.)

# Crystallographic Notation: **Planes**

**HW-2**

Notation	Interpretation
$(h\ k\ l)$	crystal <b>plane</b>
$\{h\ k\ l\}$	equivalent <b>planes</b>
$[h\ k\ l]$	crystal <b>direction</b>
$\langle h\ k\ l \rangle$	equivalent <b>directions</b>



***h***: inverse x-intercept of plane  
***k***: inverse y-intercept of plane  
***l***: inverse z-intercept of plane

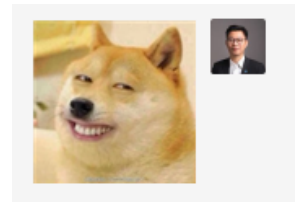
Why the **Miller indices** of this plane is **(010)**?



## 2.2 Crystal Structures

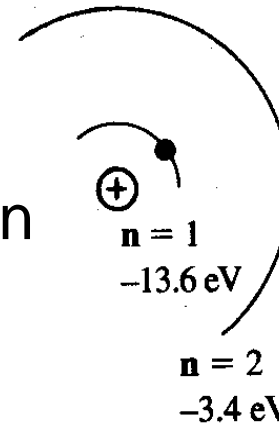
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- General material properties
- Crystal structures
- Crystallographic notation
- **Bohr's theory – energy level & band**



# Bohr's Theory

- The **electrons** of an atom can only stay on a number of **orbits**. The radius of orbits changes **discontinuously**.
- For example, **hydrogen atom**,



$n = 3$   
 $E_H = -1.51 \text{ eV}$

Next-highest level  
(excited electrons)

Outer-most electrons  
(Valence electrons)

Nucleus

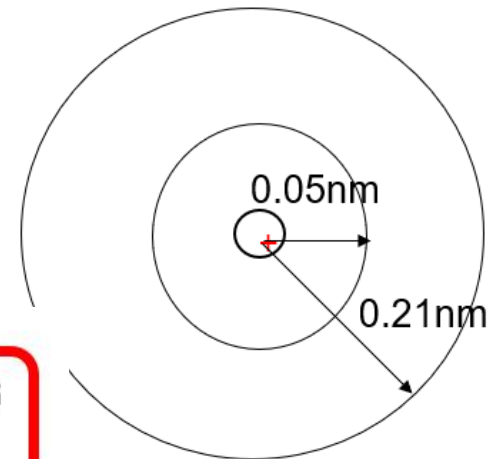
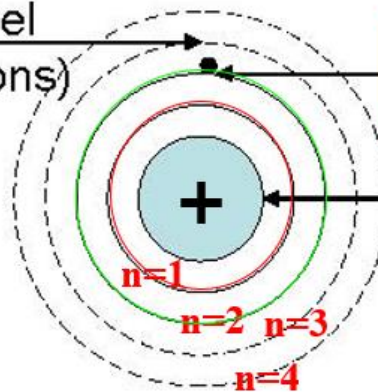
(+charge= $Zq$ )

$n=1$ : 1**s**

$n=2$ : 2**s**, 2**p**

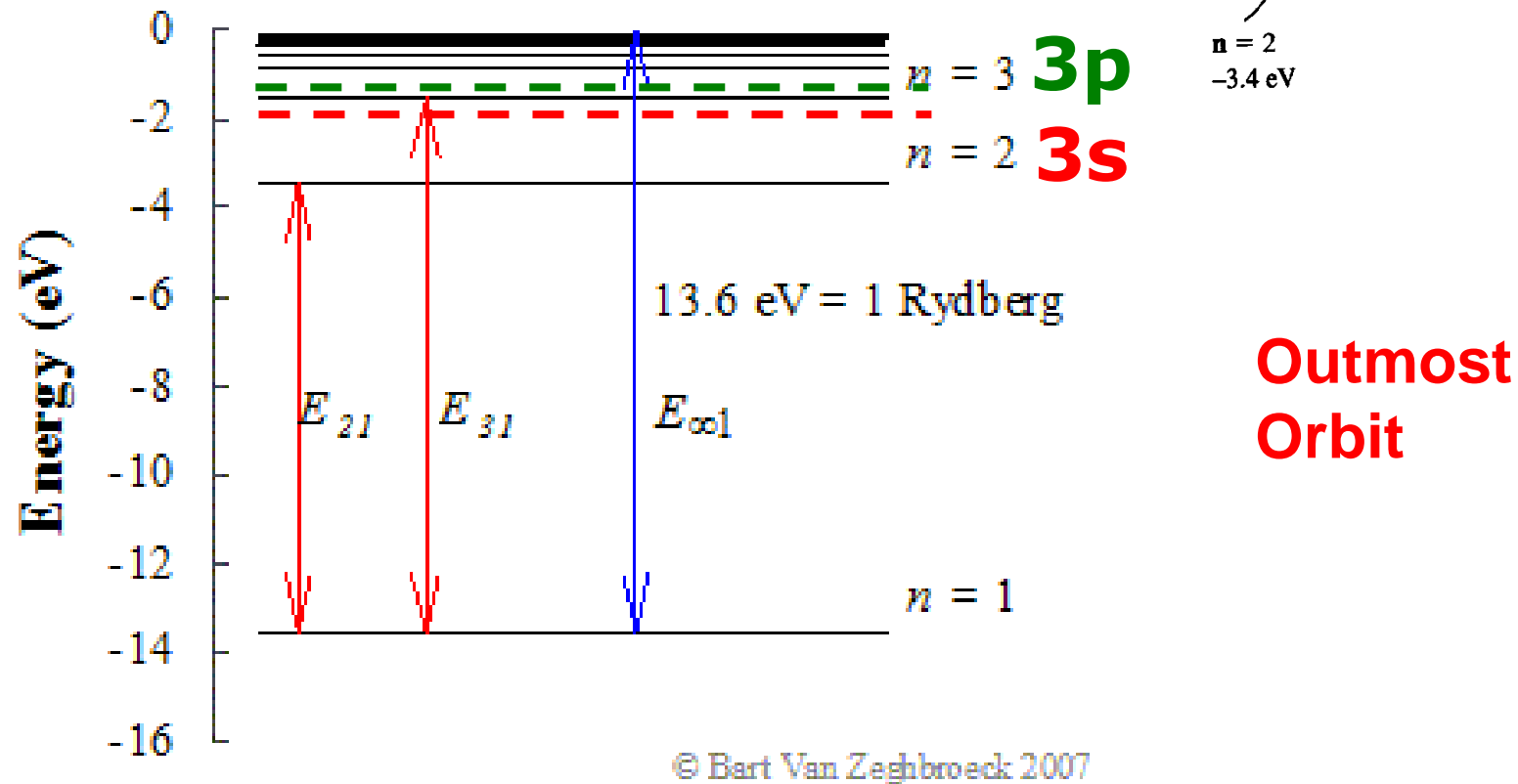
$n=3$ : 3**s**, 3**p**, 3**d**

$n=4$ : 4**s**, 4**p**, 4**d**, 4**f**



**PL**

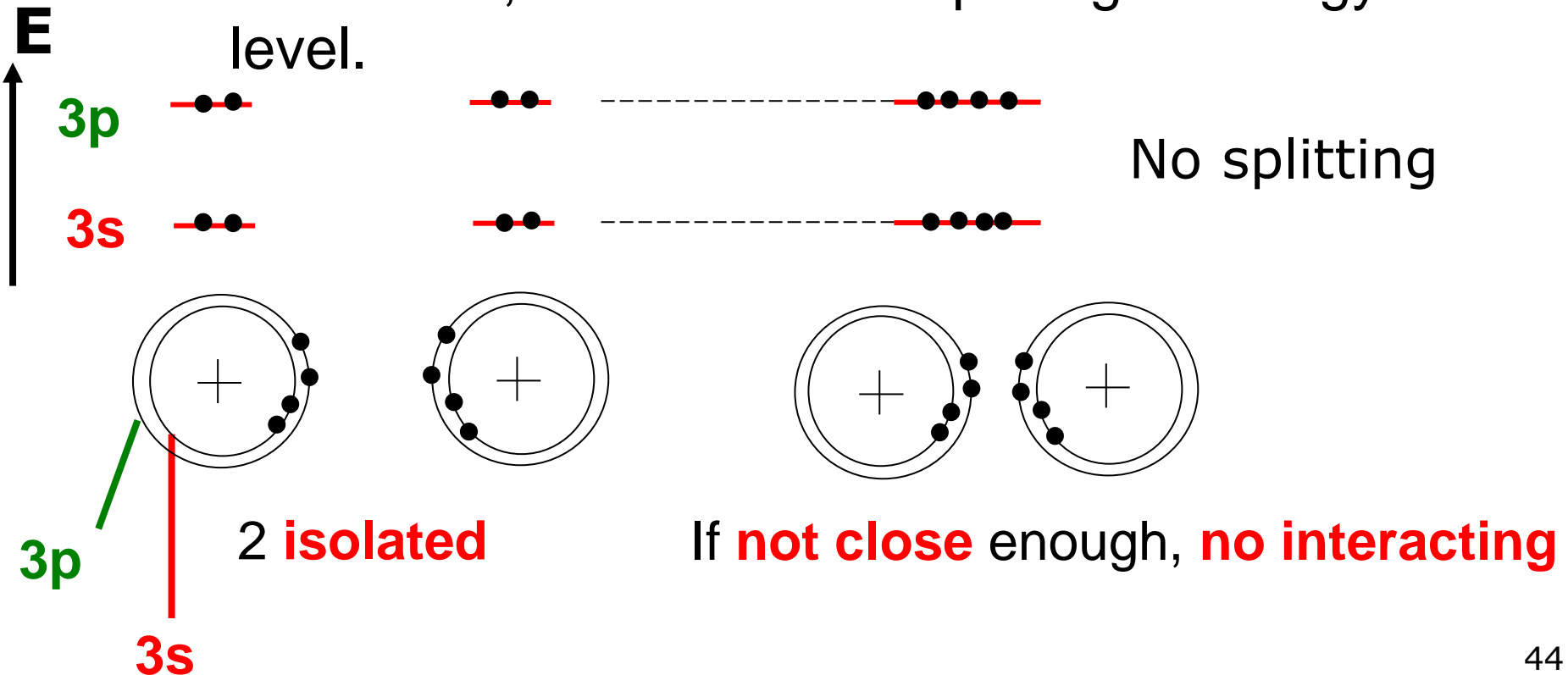
# The Bohr model



Energy levels and possible electronic transitions in a hydrogen atom. Shown are the first six energy levels, as well as three possible transitions involving the lowest energy level ( $n = 1$ )

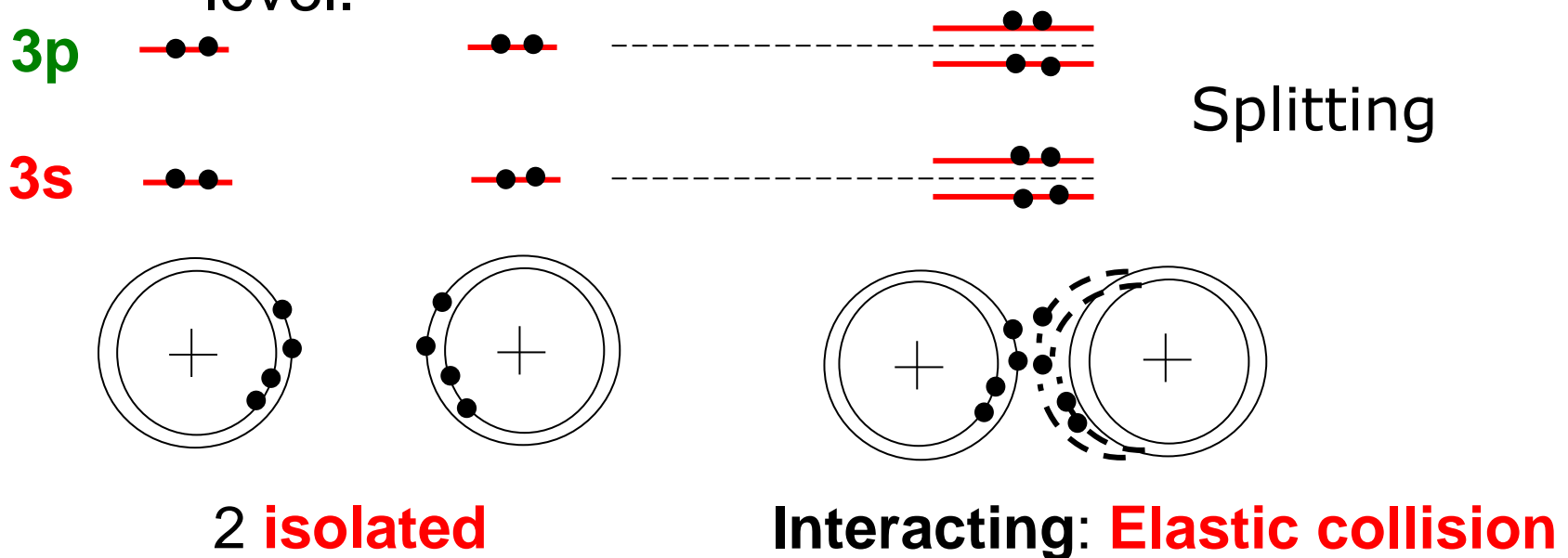
# Energy Bands

- **Energy level** of an isolated atom
- In solids, atoms interact with each other
- The orbits of electrons will be altered by interaction, which leads to splitting in energy level.



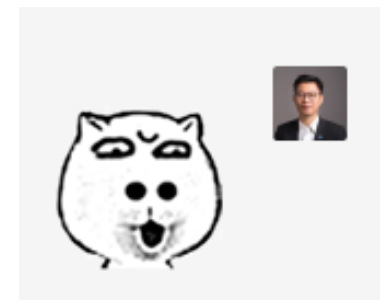
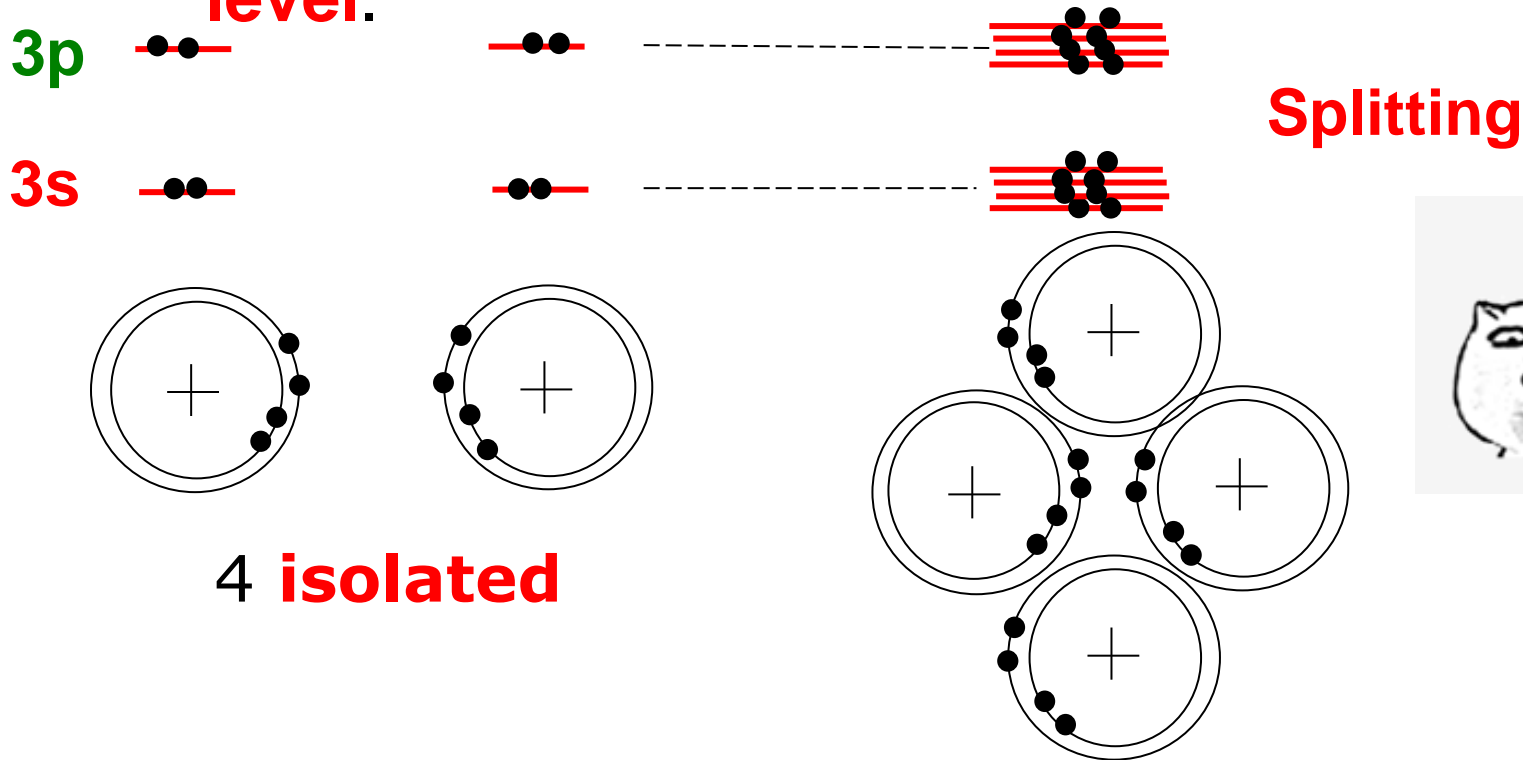
# Energy Bands

- Energy level of an isolated atom
- In solids, **atoms interact with each other**
- The orbits of electrons will be altered by interaction, which leads to splitting in energy level.

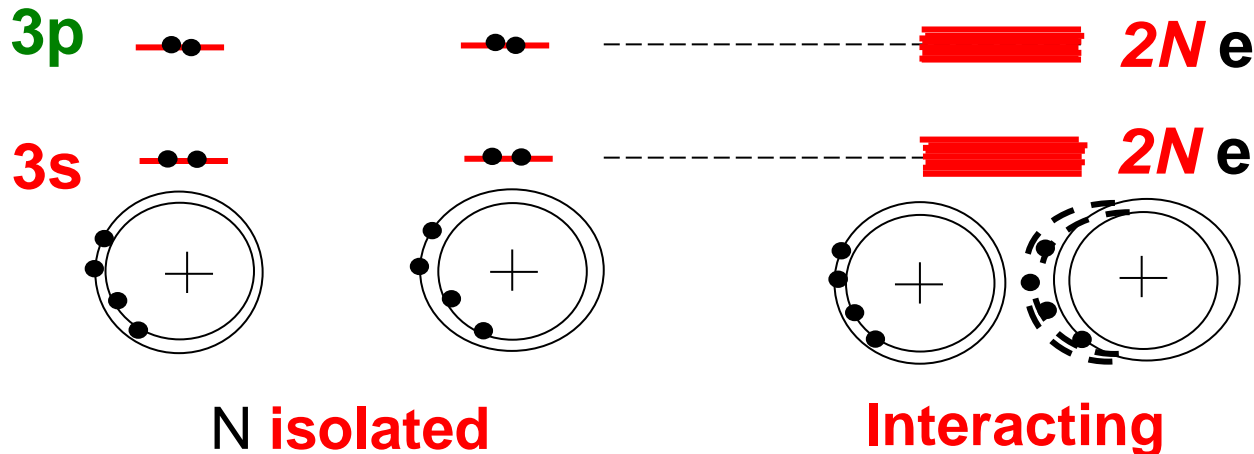
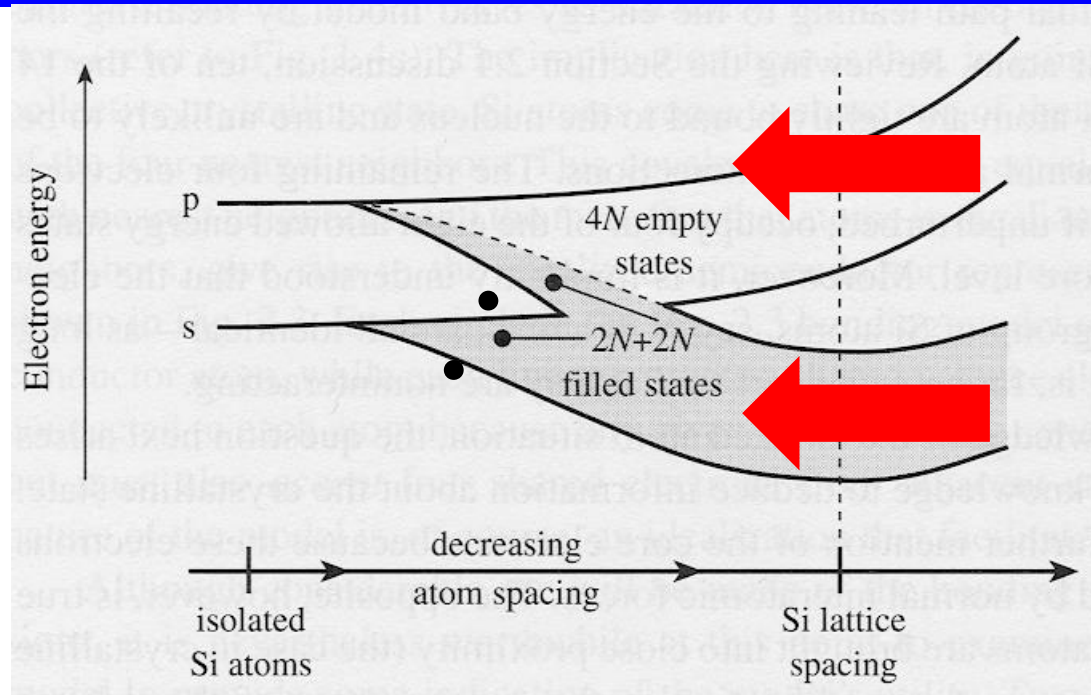


# Energy Bands

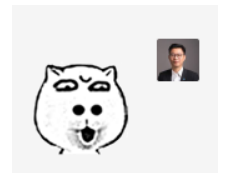
- Energy level of an isolated atom
- In solids, atoms interact with each other
- The **orbits of electrons** will be **altered** by interaction, which leads to **splitting in energy level**.



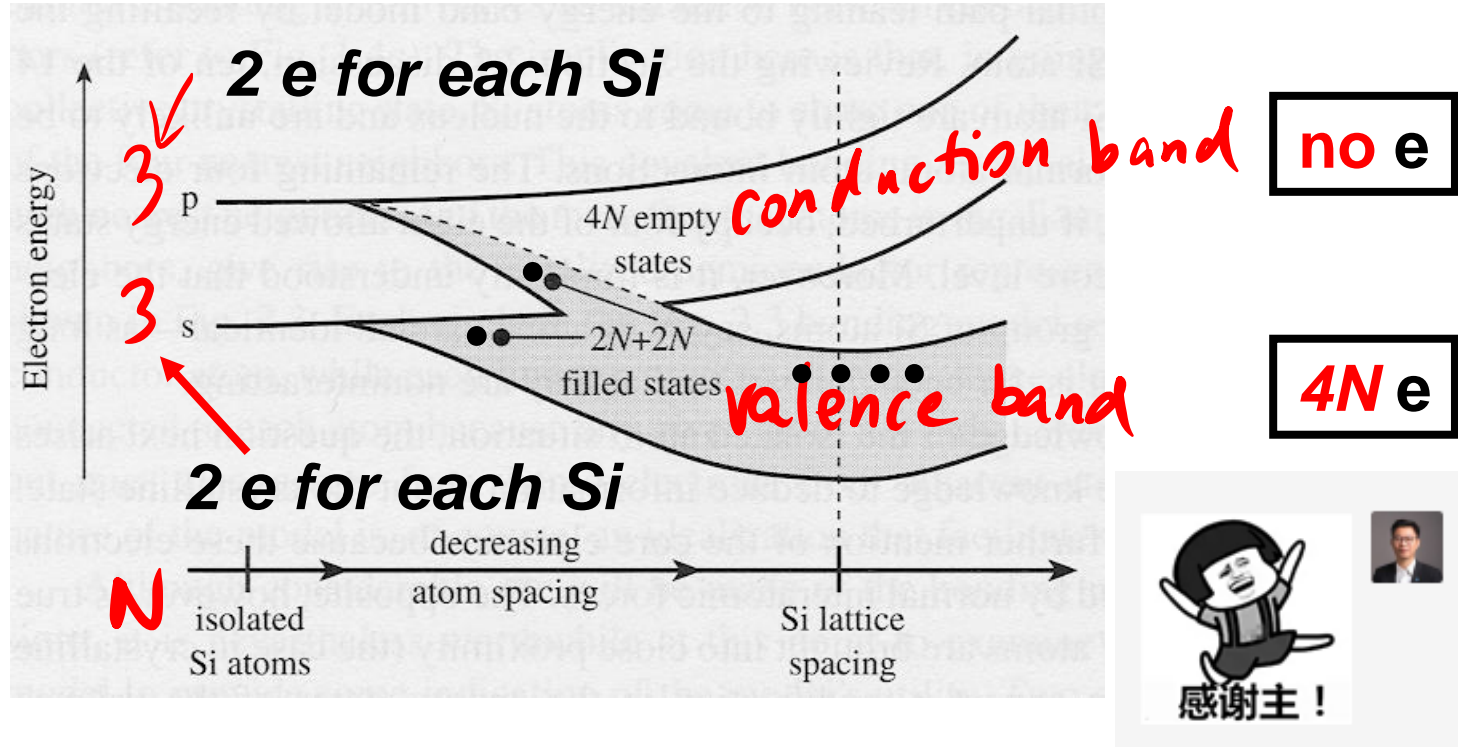
# Si: From Atom to Crystal



**Splitting**



# Si: From Atom to Crystal



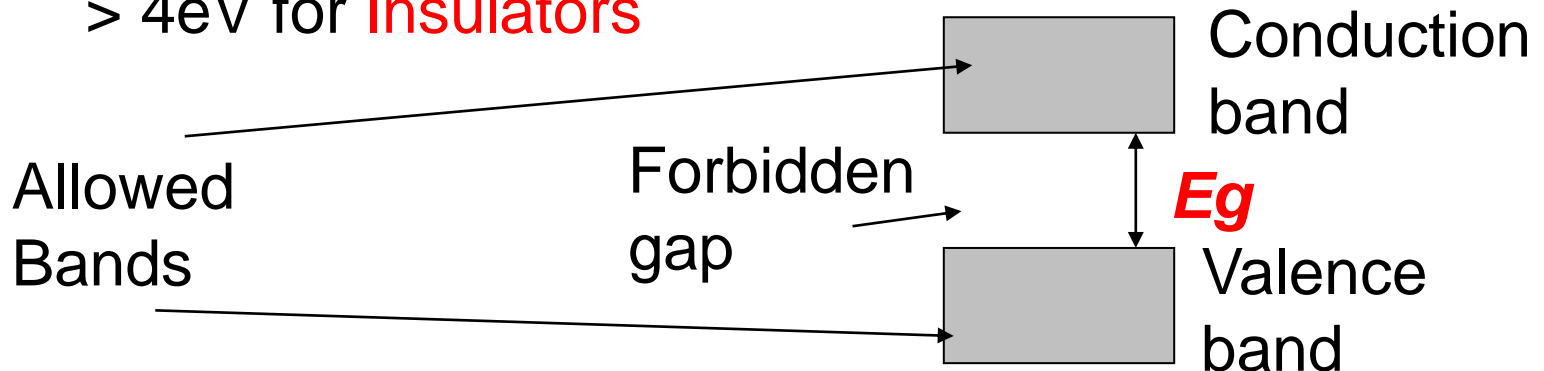
Energy **levels** in Si **atom** → **energy bands** in Si **crystal**

- The highest nearly-filled band is the valence band
- The lowest nearly-empty band is the conduction band

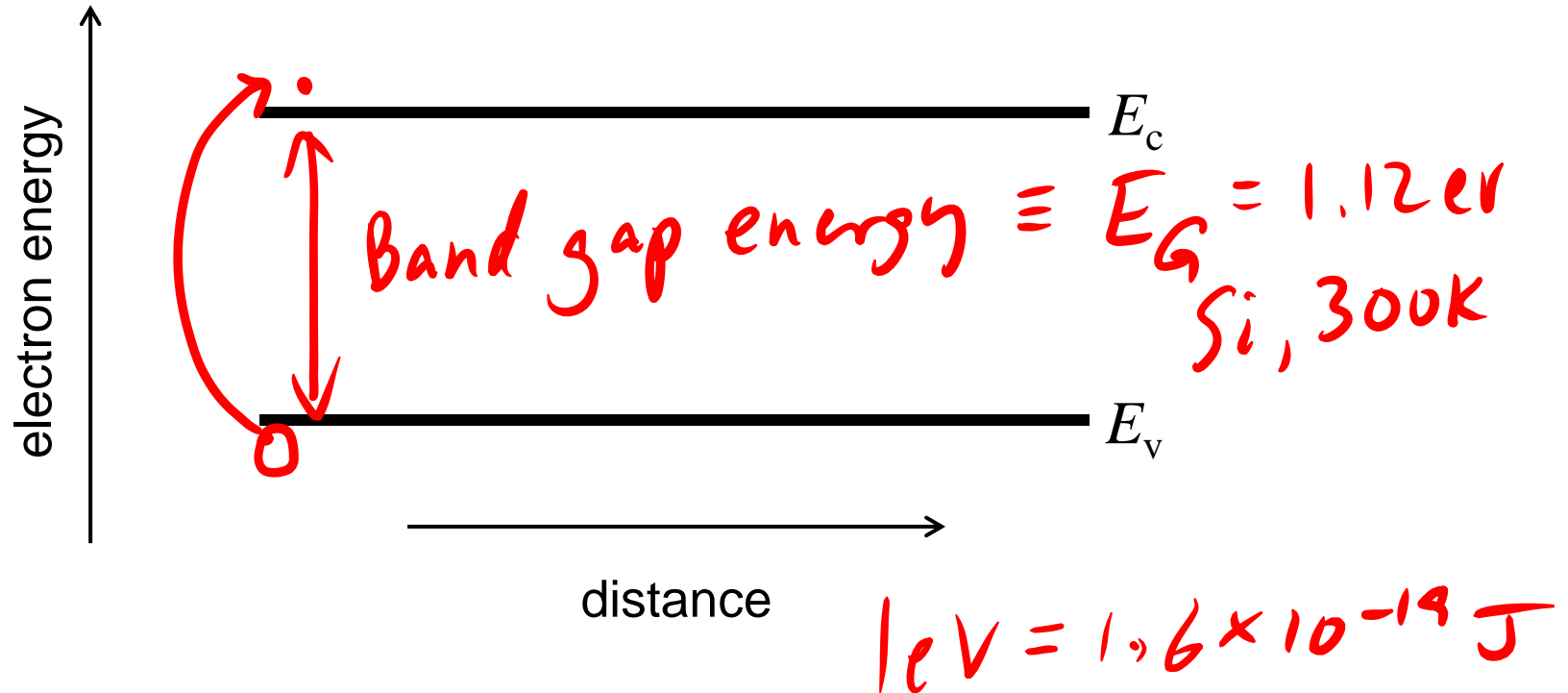


# Formation of **Energy Bands**

- **Many atom interactions** form **energy bands**.
- **Valence band**: where **valence electrons** stay
- **Conduction band**: where **free electrons** stay
- ***E<sub>g</sub>***: The **minimum energy** required to free an electron from an atom.
  - $E_g \approx 0$  for metals (**Conductors**)
  - $E_g = 1.12\text{eV}$  for Si (**Semiconductors**)
  - $> 4\text{eV}$  for **Insulators**



# Energy Band Diagram



Simplified version of energy band model, indicating

- bottom edge of the conduction band ( $E_c$ )
- top edge of the valence band ( $E_v$ )
- $E_c$  and  $E_v$  are separated by the **band gap energy  $E_g$**

# Summary of Section 2.1 & 2.2

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- **Crystalline Si:**
  - **4 valence electrons** per atom
  - **Diamond lattice**
    - each atom has 4 nearest neighbors
  - $5 \times 10^{22}$  atoms/cm<sup>3</sup>
- **Crystallographic notation**
  - **Miller indices** are used to designate **planes** and **directions** within a crystalline lattice
- ***Ec, Ev and Eg***

# Outline

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## Semiconductor Fundamentals-(I)

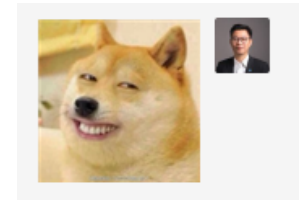
2.1 Atomic structures

2.2 Crystal structures

## Semiconductor Fundamentals-(II)

2.3 Energy bands

2.4 The doping of semiconductors



## Semiconductor Fundamentals-(III)

2.5 Boltzmann approximation &  $E_F$ ,  $n$ ,  $p$

2.6 Carrier drift and diffusion